MAGNETORESISTIVE ELEMENT AND METHOD FOR MANUFACTURING THE SAME

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a magnetoresistive element used in a magnetic head for magnetic recording such as a hard disk drive (HDD) and a magnetic random access memory (MRAM), and to a method for manufacturing the magnetoresistive element.

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2. Description of the Related Art

A multi-layer film that has a basic structure of ferromagnetic layer/non-magnetic layer/ferromagnetic layer can provide a magnetoresistance effect when current flows across the non-magnetic layer. A spin tunnel effect can be obtained when using a tunnel insulating layer as the non-magnetic layer, and a CPP (current perpendicular to the plane) GMR effect can be obtained when using a conductive metal layer of Cu or the like as the non-magnetic layer. Both magnetoresistance effects (MR effects) depend on the magnitude of a relative angle between magnetizations of the ferromagnetic layers that sandwich the non-magnetic layer. The spin tunnel effect is derived from a change in transition probability of tunnel electrons flowing between the two magnetic layers with the relative angle of magnetizations. The CPP-GMR effect is derived from a change in spin-dependent scattering.

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When a magnetoresistive element is used in a device, particularly in a magnetic memory such as MRAM, a monolithic structure combining the magnetoresistive element and a conventional Si semiconductor is necessary in view of cost and the degree of integration.

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To remove defects in wiring, a Si semiconductor process includes heat treatment at high temperatures. This heat treatment is performed, e.g., in hydrogen at about 400°C to 450°C. However, the MR characteristics of the magnetoresistive element are degraded under heat treatment at 300°C to 350°C or more.

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A method for incorporating the magnetoresistive element after formation of the semiconductor element also has been proposed. However, this method requires that wiring or the like for applying a magnetic field to the magnetoresistive element should be formed after producing the magnetoresistive element. Therefore, heat treatment is needed eventually, or a variation in wiring resistance is caused to degrade reliability and stability of the element.

SUMMARY OF THE INVENTION

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A first magnetoresistive element of the present invention includes a substrate and a multi-layer film formed on the substrate. The multi-layer film includes a pair of ferromagnetic layers and a non-magnetic layer sandwiched between the pair of ferromagnetic layers. A resistance value depends on a relative angle formed by the magnetization directions of the pair of ferromagnetic layers. The magnetoresistive element is produced by a method including heat treatment of the substrate and the multi-layer film at 330°C or more, in some cases 350°C or more, and in other cases 400°C or more. In this magnetoresistive element, when a centerline is defined so as to divide the non-magnetic layer into equal parts in the thickness direction, the longest distance R1 from the centerline to the interfaces between the pair of ferromagnetic layers and the non-magnetic layer is not more than 20 nm, and preferably not more than 10 nm.

Here, the longest distance R1 is determined by defining ten centerlines, each of which has a length of 50 nm, measuring the distances from the ten centerlines to the interfaces so as to find the longest distance for each of the ten centerlines, taking eight values except for the maximum and the minimum values from the ten longest distances, and calculating an average of the eight values.

The present invention also provides a method suitable for manufacturing the first magnetoresistive element. This method includes the following steps: forming a part of the multi-layer film other than the ferromagnetic layers and the non-magnetic layer on the substrate as an underlying film; heat-treating the underlying film at 400°C or more; decreasing roughness of the surface of the underlying film by irradiating the surface with an ion beam; forming the remaining part of the multi-layer film including the ferromagnetic layers and the non-magnetic layer on the surface; and heat-treating the substrate and the multi-layer film at 330°C or more, in some cases 350°C or more, and in other cases 400°C or more.

A second magnetoresistive element of the present invention includes a substrate and a multi-layer film formed on the substrate. The multi-layer film includes a pair of ferromagnetic layers and a non-magnetic layer sandwiched between the pair of ferromagnetic layers. A resistance value depends on a relative angle formed by the magnetization directions of the pair of ferromagnetic layers. The magnetoresistive element is produced by a method including heat treatment of the substrate and the multi-layer film at 330°C or more, in some cases 350°C or more, and in other cases 400°C or more. In this magnetoresistive element, a composition in the range that extends by 2 nm from at least one of the interfaces between the pair of ferromagnetic layers and the non-magnetic layer in the direction opposite to the non-magnetic layer is expressed by

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(FexCoyNiz)pM¹qM²rM³sAt

where M^1 is at least one element selected from the group consisting of Tc, Re, Ru, Os, Rh, Ir, Pd, Pt, Cu, Ag and Au, M^2 is at least one element selected from the group consisting of Mn and Cr, M^3 is at least one element selected from the group consisting of Ti, Zr, Hf, V, Nb, Ta, Mo, W, Al, Si, Ga, Ge, In and Sn, A is at least one element selected from the group consisting of B, C, N, O, P and S, and x, y, z, p, q, r, s, and t satisfy the following equations: $0 \le x \le 100$, $0 \le y \le 100$, $0 \le z \le 100$, x + y + z = 100, $40 \le p \le 99.7$, $0.3 \le q \le 60$, $0 \le r \le 20$, $0 \le s \le 30$, $0 \le t \le 20$, and $0 \le t \le 20$, and $0 \le t \le 20$, and $0 \le t \le 20$.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1A to 1C are cross-sectional views illustrating the longest distance R1.

FIG. 2 is a plan view showing an embodiment of a magnetoresistive element of the present invention.

FIG. 3 is a cross-sectional view showing an embodiment of a magnetoresistive element of the present invention.

FIG. 4 is a cross-sectional view showing an example of the basic configuration of a magnetoresistive element of the present invention.

FIG. 5 is a cross-sectional view showing another example of the basic configuration of a magnetoresistive element of the present invention.

FIG. 6 is a cross-sectional view showing yet another example of the basic configuration of a magnetoresistive element of the present invention.

FIG. 7 is a cross-sectional view showing still another example of the basic configuration of a magnetoresistive element of the present invention.

FIG. 8 is a cross-sectional view showing still another example of the

basic configuration of a magnetoresistive element of the present invention.

FIG. 9 is a cross-sectional view showing still another example of the basic configuration of a magnetoresistive element of the present invention.

FIG. 10 is a cross-sectional view showing still another example of the basic configuration of a magnetoresistive element of the present invention.

FIG. 11 is a cross-sectional view showing still another example of the basic configuration of a magnetoresistive element of the present invention.

FIGS. 12A to 12D are cross-sectional views each showing a portion of a magnetoresistive element produced in examples.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

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The experiments proved that heat treatment at high temperatures degrades flatness of the interfaces of a non-magnetic layer, and there is correlation between the flatness and the MR characteristics of an element. When an underlying film is processed and/or the composition in the vicinity of either of the interfaces is adjusted so as to reduce roughness of the interfaces of the non-magnetic layer after heat treatment, the MR characteristics of the element can be improved.

Among the types of "roughness" of the interfaces of the non-magnetic layer, the "roughness" that occurs in a relatively short period exerts a large effect on the MR characteristics. As shown in FIG. 1A, "waviness" may be generated on interfaces 21, 22 between ferromagnetic layers 13, 15 and a non-magnetic layer 14. The waviness can be expressed by a large radius of curvature R. However, the "waviness" as illustrated in FIG. 1A hardly affects the MR characteristics because of its long pitch. For more clear understanding of the relationship with the MR characteristics of an element, it is desirable to evaluate the state of the interfaces in the range of about 50 nm.

As shown in FIG. 1B, this specification defines a centerline 10 so as to divide the non-magnetic layer 14 into equal parts in the thickness direction and uses this centerline 10 as a reference line to understand the relationship with the MR characteristics. This method makes it possible to evaluate the state of the two interfaces 21, 22 at the same time.

Specifically, the centerline 10 can be defined by a least-square method. As enlarged in FIG. 1C, this method takes into account a distance PiQi between a point Pi on the centerline 10 and an intersection point Qi of a normal 20 to

the centerline 10 that goes through the point Pi and the interface 21, and a distance PiRi between the point Pi and an intersection point Ri of the normal 20 and the interface 22. The centerline 10 is defined so as to minimize $\int (PiQi)^2 dx$ under the condition that the sum of the square of PiQi is equal to that of PiRi $\int (PiQi)^2 dx = \int (PiRi)^2 dx$.

By defining the centerline 10 in this manner, the longest distance L between the centerline 10 and the interfaces 21, 22 can be determined in accordance with the centerline 10. To eliminate measurement errors as much as possible, this specification determines ten longest distances L for each of ten arbitrarily defined centerlines, takes eight distances L except for the maximum and the minimum values (L_{max} , L_{min}), calculates an average of the eight distances L, and uses this average as a measure R1 of evaluation.

This measurement may be performed based on a cross-sectional image of a transmission electron microscope (TEM). Simple evaluation also can be performed in the following manner: a model film is prepared by stopping the film forming process after the non-magnetic layer is deposited; the model film is subjected to in-situ heat treatment in the atmosphere of a reduced pressure; and the surface shape is observed with an atomic force microscope while maintaining the state of the film.

As long as the studies conducted, the evaluation with R1 is most suitable for understanding the relationship between the MR characteristics and the flatness of the non-magnetic layer. However, this relation may be explained better by the evaluation based on the minimum radius of curvature of the interfaces. At present, there is a limit to controlling the thickness of a sample for TEM observation. Therefore, except for a portion having a sufficiently small thickness, the interfaces tend to be overlapped in the thickness direction. Thus, it is impossible to clearly specify the minimum radius of curvature of a sample having a particularly small minimum radius of curvature. Depending on the progress in technique of producing samples for TEM observation, however, more appropriate evaluation criteria may be provided. For example, the minimum radius of curvature is measured at ten portions in the range of 50 to 100 nm, and eight values except for the maximum and the minimum values are taken to calculate an average in the same manner as described above.

The flatness of the non-magnetic layer is affected by the state of an underlying film on which a multi-layer structure is formed. In the multi-layer structure, the non-magnetic layer is positioned between the

ferromagnetic layers (ferromagnetic layer/non-magnetic layer/ferromagnetic layer). When the multi-layer film further includes lower and upper electrodes that sandwich a pair of ferromagnetic layers, the underlying film includes the lower electrode. The lower electrode often has a relatively large thickness, e.g., about 100 nm to 2 μ m. Therefore, the thickness of the underlying film, which has at least a portion formed with the lower electrode, is increased. The surface flatness of the underlying film with an increased thickness and the distortion in layers tend to affect the flatness of the non-magnetic layer to be formed on the underlying film.

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The lower electrode is not limited to a single-layer film and may be a multi-layer film formed with a plurality of conductive films.

It is preferable that the underlying film is heat-treated at 400°C or more and preferably 500°C or less. This heat treatment can reduce the distortion of the underlying film. The heat treatment is not particularly limited and may be performed in the atmosphere of a reduced pressure or inert gas such as Ar.

The surface roughness of the underlying film can be suppressed by ion-milling the surface at a low angle or irradiating it with a gas cluster ion beam. The ion beam irradiation may be performed so that the angle of incidence of the ion beam at the surface of the underlying film is 5° to 25°. Here, the angle of incidence is 90° when the ion beam orients perpendicular to the surface and is 0° when it orients parallel to the surface.

Considering, e.g., the growth of crystal grains due to heat treatment, the process of decreasing roughness by ion beam irradiation should be performed after the heat treatment. The surface irradiated with the ion beam preferably is a plane on which the ferromagnetic layer is formed directly. However, it can be a plane for supporting the ferromagnetic layer via other layers.

The use of a single-crystal substrate makes it easy to produce an element having a low R1. There are some cases where an element having a small R1 can be obtained, e.g., by irradiating the lower electrode layer with an ion beam even if the single-crystal substrate is not used.

The flatness of the non-magnetic layer is affected also by the composition of the ferromagnetic layers in the vicinity of either of the interfaces of the non-magnetic layer.

Specifically, in the range of 2 nm, preferably in the range of 4 nm, from at least one of the interfaces between a pair of ferromagnetic layers

and the non-magnetic layer, the composition of the ferromagnetic layer in contact with the at least one of the interfaces is expressed by

(FexCoyNiz)pM¹qM²rM³sAt

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where M¹ is at least one element selected from the group consisting of Tc, Re, Ru, Os, Rh, Ir, Pd, Pt, Cu, Ag and Au, preferably Ir, Pd and Pt, M² is at least one element selected from the group consisting of Mn and Cr, M³ is at least one element selected from the group consisting of Ti, Zr, Hf, V, Nb, Ta, Mo, W, Al, Si, Ga, Ge, In and Sn, and A is at least one element selected from the group consisting of B, C, N, O, P and S.

Also, x, y, z, p, q, r, s, and t satisfy $0 \le x \le 100$, $0 \le y \le 100$, $0 \le z \le 100$, x + y + z = 100, $40 \le p \le 99.7$, $0.3 \le q \le 60$, $0 \le r \le 20$, $0 \le s \le 30$, $0 \le t \le 20$, and p + q + r + s + t = 100.

In the above equations, p, q, and r may satisfy p + q + r = 100 (s = 0, t = 0), and also p and q may satisfy p + q = 100 (s = 0, t = 0, r = 0).

When the element M¹ is included in the vicinity of either of the interfaces with the non-magnetic layer, a small R1 can be achieved easily. There are some cases where the MR characteristics after heat treatment at 330°C or more are even more improved than those before the heat treatment by addition of the element M¹. The effects of the element M¹ are not clarified fully at present. Since these elements have a catalytic effect on oxygen or the like, the state of bonding between non-magnetic compounds that constitute the non-magnetic layer is enhanced, which may lead to an improvement in barrier characteristics.

When the content of the element M^1 is more than 60 at% (q > 60), the function as a ferromagnetic material in the ferromagnetic layer is reduced, thus degrading the MR characteristics. The preferred content of the element M^1 is 3 to 30 at% ($3 \le q \le 30$).

The element M^2 is oxidized easily and becomes an oxide having magnetism after oxidation. The element M^2 may be used for an antiferromagnetic layer. When the element M^2 is diffused to the vicinity of either of the interfaces with the non-magnetic layer by heat treatment, it forms an oxide in the vicinity of either of the interfaces. This may cause degradation of the characteristics. However, when the element M^2 is not more than 20 at% ($r \le 20$) and is present with the element M^1 , the MR characteristics are not degraded significantly. In particular, when the

content of the element M^2 is smaller than that of the element M^1 (q > r), there are some cases where the MR characteristics are improved rather than degraded. When added with the element M^1 (q > 0, r > 0), the element M^2 may contribute to the improvement in MR characteristics after heat treatment.

When the magnetoresistive element is used in a device, the magnetic characteristics, such as soft magnetic properties and high-frequency properties, become important other than the MR characteristics. In this case, the element M³ and the element A should be added appropriately within the above range.

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The ratio of Fe, Co, and Ni is not particularly limited, as long as the total content is 40 to 99.7 at%. However, in the presence of all the three elements, it is preferable to establish 0 < x 100, 0 < y < 100, $0 < z \le 90$ (particularly, $0 < z \le 65$). In the case of a two-component system of Fe and Co (z = 0), it is preferable to establish $5 \le x < 100$ and $0 < y \le 95$. In the case of a two-component system of Fe and Ni (y = 0), it is preferable to establish $5 \le x < 100$ and $0 < z \le 95$.

To analyze the composition, a local composition analysis using, e.g., TEM may be preformed. A model film obtained by stopping the film forming process after the non-magnetic layer is deposited may be used as the ferromagnetic layer located below the non-magnetic layer. In this case, the model film is heat-treated at a predetermined temperature, then the non-magnetic layer is removed appropriately by milling, and thus the composition is measured with surface analysis such as Auger electron spectroscopy and XPS composition analysis.

FIGS. 2 and 3 show the basic configuration of a magnetoresistive element. This element includes a lower electrode 2, a first ferromagnetic layer 3, a non-magnetic layer 4, a second ferromagnetic layer 5, and an upper electrode 6 in this order on a substrate 1. A pair of electrodes 2, 6 that sandwich a laminate of ferromagnetic layer/non-magnetic layer/ferromagnetic layer are isolated by an interlayer insulating film 7.

The film configuration of the magnetoresistive element is not limited to the above, and other layers can be added further as shown in FIGS. 4 to 11. If necessary, lower and upper electrodes are arranged respectively below and above the laminate shown, though these drawings omit both electrodes. Other layers that are not illustrated in the drawings (e.g., an underlying layer and a protective layer) also can be added.

As shown in FIG. 4, an antiferromagnetic layer 8 is formed in contact with a ferromagnetic layer 3. In this element, the ferromagnetic layer 3 shows unidirectional anisotropy due to an exchange bias magnetic field with the antiferromagnetic layer 8, and thus the reversing magnetic field becomes larger. By adding the antiferromagnetic layer 8, the element becomes a spin-valve type element, in which the ferromagnetic layer 3 functions as a pinned magnetic layer and the ferromagnetic layer 5 functions as a free magnetic layer.

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As shown in FIG. 5, a laminated ferrimagnetic material may be used as a free magnetic layer 5. The laminated ferrimagnetic material includes a pair of ferromagnetic layers 51, 53 and a non-magnetic metal film 52 sandwiched between the ferromagnetic layers.

As shown in FIG. 6, the element may be formed as a dual spin-valve type element. In this element, two pinned magnetic layers 3, 33 are arranged so as to sandwich a free magnetic layer 5, and non-magnetic layers 4, 34 are located between the free magnetic layer 5 and the pinned magnetic layers 3, 33.

As shown in FIG. 7, laminated ferrimagnetic materials 51, 52, 53; 71, 72, 73 may be used as pinned magnetic layers 3, 33 in the dual spin-valve type element. In this element, antiferromagnetic layers 8, 38 are arranged in contact with the pinned magnetic layers 3, 33.

As shown in FIG. 8, a laminated ferrimagnetic material may be used as the pinned magnetic layer 3 of the element in FIG. 4. The laminated ferrimagnetic material includes a pair of ferromagnetic layers 51, 53 and a non-magnetic metal film 52 sandwiched between the ferromagnetic layers.

As shown in FIG. 9, the element may be formed as a differential coercive force type element that does not include an antiferromagnetic layer. In this element, a laminated ferrimagnetic material 51, 52, 53 is used as a pinned magnetic layer 3.

As shown in FIG. 10, a laminated ferrimagnetic material 71, 72, 73 may be used as the free magnetic layer 5 of the element in FIG. 8.

As shown in FIG. 11, a pinned magnetic layer 3(33), a non-magnetic layer 4(34), and a free magnetic layer 5(35) may be arranged on both sides of an antiferromagnetic layer 8. In this element, a laminated ferrimagnetic material 51(71), 52(72), 53(73) is used as the pinned magnetic layer 3(33).

As the substrate 1, a plate with an insulated surface, e.g., a Si substrate obtained by thermal oxidation, a quartz substrate, and a sapphire

substrate can be used. Since the substrate surface should be smoother, a smoothing process, e.g., chemomechanical polishing (CMP) may be performed as needed. A switching element such as an MOS transistor may be produced on the substrate surface beforehand. In this case, it is preferable that an insulating layer is formed on the switching element, and then contact holes are provided in the insulating layer to make an electrical connection between the switching element and the magnetoresistive element to be formed on the top.

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As the antiferromagnetic layer 8, a Mn-containing antiferromagnetic material or a Cr-containing material can be used. Examples of the Mn-containing antiferromagnetic material include PtMn, PdPtMn, FeMn, IrMn, and NiMn. The element M² may diffuse from these antiferromagnetic materials by heat treatment. Therefore, considering the preferred content (20 at% or less) of the element M² in the vicinity of the interface with the non-magnetic layer, an appropriate distance between the non-magnetic layer and the antiferromagnetic layer (indicated by d in FIG. 4) is 3nm to 50nm.

The conventionally known various materials also can be used for other layers of the multi-layer film without any limitation.

For example, a material with conductive or insulating properties can be used as the non-magnetic layer 2 in accordance with the type of the element. A conductive non-magnetic layer used in a CPP-GMR element can be made, e.g., of Cu, Au, Ag, Ru, Cr, and an alloy of these elements. The preferred thickness of the non-magnetic layer in the CPP-GMR element is 1 to 10 nm. The material for a tunnel insulating layer used in a TMR element is not particularly limited as well, and various insulators or semiconductors can be used. An oxide, a nitride, or an oxynitride of Al is suitable for the tunnel insulating layer. The preferred thickness of the non-magnetic layer in the TMR element is 0.8 to 3 nm.

Examples of a material for the non-magnetic film that constitutes the laminated ferrimagnetic material include Cr, Cu, Ag, Au, Ru, Ir, Re, Os, and an alloy and an oxide of theses elements. The preferred thickness of this non-magnetic film is 0.2 to 1.2 nm, though it varies depending on the material.

A method for forming each layer of the multi-layer film is not particularly limited, and a thin film producing method may be employed, e.g., sputtering, molecular beam epitaxy (MBE), chemical vapor deposition

(CVD), pulse laser deposition, and ion beam sputtering. As a micro-processing method, well-known micro-processing methods, such as photolithography using a contact mask or stepper, EB lithography and focused ion beam (FIB) processing, may be employed.

For etching, well-known methods, such as ion milling and reactive ion etching (RIE), may be employed.

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Even with a conventional magnetoresistive element, the MR characteristics after heat treatment sometimes is improved if the temperature is up to about 300°C. However, the MR characteristics are degraded after heat treatment at 300 to 350°C or more. A magnetoresistive element of the present invention is superior to the conventional element in characteristics after heat treatment at 330°C or more. However, such a difference in characteristics between the two elements is even more conspicuous with increasing heat treatment temperatures to 350°C or more, and 400°C or more.

Considering that the element is combined with a Si semiconductor process, the heat treatment temperature should be about 400°C. The present invention can provide an element that exhibits practical characteristics even for heat treatment at 400°C.

As described above, the present invention can provide a magnetoresistive element in which the MR characteristics are improved by heat treatment at 330°C or more and also 350°C or more, compared with the MR characteristics without heat treatment.

The reason for an improvement in MR characteristics by heat treatment is not clarified fully. However, the heat treatment may improve the barrier characteristics of the non-magnetic layer. This is because favorable MR characteristics can be obtained generally by reducing defects in a barrier or increasing the height of the barrier. Another possible reason is a change in chemical bond at the interfaces between the non-magnetic layer and the ferromagnetic layers. In either case, it is very important to achieve the effect of improving the MR characteristics even after heat treatment at 300°C or more, considering the application of a magnetoresistive element to a device.

A composition that forms a single phase at heat treatment temperatures is suitable for the composition of the ferromagnetic layer in the vicinity of the interface.

An alloy having the same composition as that at the interfaces was

molded by general molding, which then was heat-treated in inert gas at 350°C to 450°C for 24 hours. This alloy was cut substantially in half, and then the cutting planes were polished and etched. The state of particles on the surface was observed with a metallurgical microscope and an electron microscope. Moreover, the composition distribution was evaluated by the above composition analysis or EDX. The result confirmed that when a composition showed a nonuniform phase at heat treatment temperatures used, there was a high probability of degradation in MR characteristics after heat treatment for a long time.

A bulk differs from a thin film in phase stability depending on the effect of the interfaces. However, it is preferable that the composition of the ferromagnetic layers in the vicinity of each of the interfaces, specifically the composition given by the above equation, forms a single phase at predetermined heat treatment temperatures of 330°C or more.

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Example 1-1

A Pt film having a thickness of 100 nm was evaporated on a single-crystal MgO (100) substrate as a lower electrode with MBE, which then was heat-treated in vacuum at 400°C for 3 hours. The substrate was irradiated with Ar ions at an incidence angle of 10° to 15° by using an ion gun, thus cleaning the surface and decreasing roughness on the surface.

Next, a NiFe film having a thickness of 8 nm was formed on the Pt film with RF magnetron sputtering. Further, an Al film formed with DC magnetron sputtering was oxidized by introducing pure oxygen into a vacuum chamber so as to produce an AlOx barrier. Subsequently, a $Fe_{50}Co_{50}$ film having a thickness of 10 nm was formed with RF magnetron sputtering. Thus, a laminate of ferromagnetic layer/non-magnetic layer/ferromagnetic layer (NiFe(8)/AlOx(1.2)/Fe₅₀Co₅₀(10)) was formed on the lower electrode. Here, the figures in parentheses denote the film thickness in nm (the film thickness is expressed in the same manner in the following).

With patterning by photolithography and ion milling etching, a plurality of magnetoresistive elements having the same configuration as that shown in FIGS. 1 and 2 were produced. A Cu film was formed as an upper electrode with DC magnetron sputtering, and a SiO₂ film was formed as an interlayer insulating film with ion beam sputtering.

The MR ratio of each of the magnetoresistive elements was

measured by measuring a resistance with a DC four-terminal method while applying a magnetic field. The MR ratio was measured after each of the heat treatments at 260°C for 1 hour, at 300°C for 1 hour, at 350°C for 1 hour, and at 400°C for 1 hour. After measurement of the MR ratio, R1 was measured for each element. Table 1A shows the results.

TABLE 1A

r					
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
No heat	MR(%) (average/max)	12/13.5	11.9/13.2	10.5/12.8	8.2/-
treatment	Number of	80	12	6	1
	corresponding samples				
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
260°C	MR(%) (average/max)	14.1/15.2	13.8/14.8	12.5/13.2	8.5/9.2
-260 C	Number of	82	12	3	3
	corresponding samples				
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
300°C	MR(%) (average/max)	15.8/16.0	15.5/15.9	14.5/14.9	2.1/9.2
300 C	Number of	62	15	9	12
	corresponding samples	·			
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
350°C	MR(%) (average/max)	16.2/16.4	15.7/16.0	14.5/14.9	1.9/5.2
990 C	Number of	17	14	26	33
	corresponding samples				
	R1 .	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
400°C	MR(%) (average/max)	16.4/16.6	15.9/16.1	14.5/14.9	1.8/2.3
400 0	Number of	3	6	15	51
,	corresponding samples				

The total number of samples varies depending on a heat treatment temperature.

10 Example 1-2

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A plurality of magnetoresistive elements were produced in the same manner as Example 1-1 except that a laminate of a NiFe film having a thickness of 6 nm and a $Fe_{80}Pt_{20}$ film having a thickness of 2 nm was used instead of the NiFe film. These elements included a laminate expressed by

NiFe(6)/Fe₈₀Pt₂₀(2)/AlOx(1.2)/Fe₅₀Co₅₀(10). The MR ratio and R1 were measured for each magnetoresistive element in the same manner as the above. Table 1B shows the results.

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TABLE 1B

	R1	R1≤3	3 <r1≤10< th=""><th>10<r1≤20< th=""><th>20<r1< th=""></r1<></th></r1≤20<></th></r1≤10<>	10 <r1≤20< th=""><th>20<r1< th=""></r1<></th></r1≤20<>	20 <r1< th=""></r1<>
No heat	MR(%) (average/max)	21.1/25.1	20.2/22.7	15.2/-	-/-
treatment	Number of	87	12	1	0
	corresponding samples				
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
260°C	MR(%) (average/max)	23.4/26.3	21.9/24.6	14.9/15.3	-/-
200 0	Number of	87	10	3 .	0
	corresponding samples				
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
300°C	MR(%) (average/max)	24.6/26.5	23.2/25.2	14.5/15.1	6.8/-
300 C	Numbér of	87	8	2	1
	corresponding samples				
	. R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
350°C	MR(%) (average/max)	25.9/26.4	24.8/25.3	14.7/14.9	5.9/-
300 C	Number of	85	. 5	2	1
,	corresponding samples		:		,
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
400°C	MR(%) (average/max)	26.6/26.9	25.1/25.2	14.1/14.6	6.2/6.6
400 0	Number of	80	4	3	2
	corresponding samples				·

The total number of samples varies depending on a heat treatment temperature.

Comparative example

For comparison, a plurality of magnetoresistive elements were
10 produced in the same manner as Example 1-1 except for the heat treatment
of electrodes and the irradiation with an ion gun. The MR ratio and R1
were measured for each magnetoresistive element in the same manner as
the above. Table 1C shows the results.

TABLE 1C

R1	R1≤3	3 <r1≤10< th=""><th>10<r1≤20< th=""><th>20<r1< th=""></r1<></th></r1≤20<></th></r1≤10<>	10 <r1≤20< th=""><th>20<r1< th=""></r1<></th></r1≤20<>	20 <r1< th=""></r1<>
MR(%) average/max)	-/-	11.8/12.5	10.4/12.6	8.1/9.1
Number of	0	3	35	62
orresponding				
samples				
R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
The state of the s	-/-	13.8/14.1	12.2/13.2	8.3/9.0
Number of	0	2	25	73
orresponding samples	·			
R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
MR(%) average/max)	·/·	٠/٠	14.1/14.7	1.9/7.3
Number of	0	0	5	91
	R1<3	3 <r1<10< td=""><td>10<r1<20< td=""><td>20<r1< td=""></r1<></td></r1<20<></td></r1<10<>	10 <r1<20< td=""><td>20<r1< td=""></r1<></td></r1<20<>	20 <r1< td=""></r1<>
MR(%)	-/-	-/-	· -/-	1.7/4.8
Number of	0	0	0	89
	D 1 -0	0.701.410	10 D1 20	00 D1
	K1≤3	3 <k1≤10< td=""><td>10<k1<u><20</k1<u></td><td>20<r1< td=""></r1<></td></k1≤10<>	10 <k1<u><20</k1<u>	20 <r1< td=""></r1<>
	-/- ·	./-	-/-	1.2/1.9
Number of	0	0	0	75
	MR(%) average/max) Number of orresponding samples R1 MR(%) average/max) Average/max) Average/max	MR(%) -/- average/max) 0 Number of orresponding samples R1 R1≤3 MR(%) -/- average/max) 0 Number of orresponding samples -/- Number of orresponding samples R1 R1≤3 MR(%) -/- average/max) Number of orresponding samples -/- R1 R1≤3 MR(%) -/- average/max) -/- Number of orresponding samples -/- R1 R1≤3 MR(%) -/- average/max) Number of orresponding orresponding -/- average/max) Number of orresponding orresponding -/-	MR(%) ·/· 11.8/12.5 average/max) ·/· 3 Number of orresponding samples R1 R1≤3 3 <r1≤10< td=""> MR(%) ·/· 13.8/14.1 Number of orresponding samples R1 R1≤3 3<r1≤10< td=""> MR(%) ·/· ·/· average/max) ·/· ·/· Number of orresponding samples R1 R1≤3 3<r1≤10< td=""> MR(%) ·/· ·/· average/max) ·/· ·/· Number of orresponding samples R1 R1≤3 3<r1≤10< td=""> MR(%) ·/· ·/· average/max) ·/· ·/· Number of orresponding ·/· ·/· average/max) Number of orresponding ·/· average/max) ·/· ·/· Number of orresponding ·/· ·/· average/max) ·/· ·/· Number of orresponding ·/· ·/· average/max) ·/· ·/·</r1≤10<></r1≤10<></r1≤10<></r1≤10<>	MR(%) average/max) -/- 11.8/12.5 10.4/12.6 Number of orresponding samples 0 3 35 R1 R1≤3 3 <r1≤10< td=""> 10<r1≤20< td=""> MR(%) average/max) -/- 13.8/14.1 12.2/13.2 Number of orresponding samples 0 2 25 MR(%) average/max) -/- -/- 14.1/14.7 Number of orresponding samples 0 0 5 R1 R1≤3 3<r1≤10< td=""> 10<r1≤20< td=""> MR(%) average/max) -/- -/- -/- Number of orresponding samples 0 0 0 0 R1 R1≤3 3<r1≤10< td=""> 10<r1≤20< td=""> MR(%) average/max) -/- -/- -/- Number of orresponding average/max) -/- -/- -/- Number of orresponding orresponding -/- -/- -/- Alexance of orresponding orresponding orresponding -/- -/- -/- Alexance of orresponding orresponding orresponding orresponding orresponding -/- -/- -/- Alexance orresponding orresponding orresponding orresponding orresponding o</r1≤20<></r1≤10<></r1≤20<></r1≤10<></r1≤20<></r1≤10<>

The total number of samples varies depending on a heat treatment temperature.

In a conventional method (Table 1C) that did not include the surface treatment of a lower electrode, all values of R1 were more than 20 nm after heat treatment at temperatures in excess of 300°C.

Table 1B shows that the addition of Pt to the magnetic layers in the vicinity of the non-magnetic layer can suppress an increase in R1 caused by heat treatment as compared with Table 1A, in which Pt is not added. Even if R1 is in the same range, the MR ratio can be improved by the addition of Pt.

Example 1-3

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A plurality of magnetoresistive elements were produced in the same manner as Example 1-1 except that a Si substrate obtained by thermal

oxidation was used as a substrate, a Cu film having a thickness of 100 nm and a Ta film having a thickness of 5 nm were used as a lower electrode, and NiFe(8)/Co₇₅Fe₂₅(2)/BN(2.0)/Fe₅₀Co₅₀(5) was used as a laminate of ferromagnetic layer/non-magnetic layer/ferromagnetic layer. Both Cu and Ta films were formed with RF magnetron sputtering, the NiFe film was formed with DC magnetron sputtering, the Co₇₅Fe₂₅ film was formed with RF magnetron sputtering, the BN film was formed with reactive evaporation, and the Fe₅₀Co₅₀ film was formed with RF magnetron sputtering.

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The MR ratio and R1 were measured for each magnetoresistive element in the same manner as the above. Table 2 shows the results.

TABLE 2

R1	R1≤3	3 <r1≤10< th=""><th>10<r1≤20< th=""><th>20<r1< th=""></r1<></th></r1≤20<></th></r1≤10<>	10 <r1≤20< th=""><th>20<r1< th=""></r1<></th></r1≤20<>	20 <r1< th=""></r1<>
MR(%) (average/max)	18.1/20.0	17.9/19.5	15.5/17.8	10.2/13.2
Number of	67	22	7	4
corresponding				
	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
MR(%) (average/max)	18.2/20.1	18.0/19.7	16.5/17.9	12.1/13.5
Number of	69	21	5	5
corresponding samples				·
R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
MR(%) (average/max)	19.5/20.3	19.1/19.9	17.5/18.8	11.8/13.5
Number of	36	36	9	15
corresponding				
samples				
R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
MR(%) (average/max)	19.7/20.5	19.2/20.2	17.5/18.8	5.8/11.8
Number of	15	16	21	36
				,
	D1 -0	0 -D1 -10	10 -D1 -00	90 .D1
	K1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
(average/max)	19.9/20.6	19.2/20.0	16.8/18.5	2.8/5.6
Number of	1	8	13	52
corresponding samples				
	MR(%) (average/max) Number of corresponding samples R1 MR(%) (average/max) Number of	MR(%) (average/max) 18.1/20.0 Number of corresponding samples 67 R1 R1≤3 MR(%) 18.2/20.1 Number of corresponding samples 69 R1 R1≤3 MR(%) 19.5/20.3 Number of corresponding samples 36 R1 R1≤3 MR(%) 19.7/20.5 Number of corresponding samples 15 R1 R1≤3 MR(%) 19.9/20.6 (average/max) 19.9/20.6 Number of corresponding 1 Number of corresponding 1 Ourseponding 1	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

The total number of samples varies depending on a heat treatment temperature.

Example 1-4

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A plurality of magnetoresistive elements were produced in the same manner as Example 1-1 except that a Si substrate obtained by thermal oxidation was used as a substrate, a Cu film having a thickness of 200 nm and a TiN film having a thickness of 3 nm were used as a lower electrode, and NiFe(8)/Co₇₅Fe₂₅(2)/AlOx(2.0)/Fe₅₀Co₅₀(5) was used as a laminate of ferromagnetic layer/non-magnetic layer/ferromagnetic layer. The AlOx film was oxidized with plasma oxidation.

The MR ratio and R1 were measured for each magnetoresistive element in the same manner as the above. Table 3 shows the results.

TABLE 3

	R1	R1≤3	3 <r1≤10< th=""><th>10<r1≤20< th=""><th>20<r1< th=""></r1<></th></r1≤20<></th></r1≤10<>	10 <r1≤20< th=""><th>20<r1< th=""></r1<></th></r1≤20<>	20 <r1< th=""></r1<>
No heat	MR(%) (average/max)	22.1/24.2	21.5/24.1	20.1/22.8	15.5/17.9
treatment	Number of	66	23	6	5
	corresponding samples				
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
1	MR(%)	11120	<u>3<1€10</u>	10~101520	20/111
260°C	(average/max)	23.1/24.5	22.8/24.3	21.8/23.0	16.0/17.2
200 C	Number of	67	20	6	7
	corresponding samples				
	R1	. R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
	MR(%) (average/max)	24.1/24.7	23.5/24.3	22.0/22.8	12.5/15.1
300°C	Number of	31	34	11	18
	corresponding		_		
	samples				
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
05000	MR(%) (average/max)	24.3/24.7	23.8/24.1	21.8/22.2	3.2/8.1
350°C	Number of	3	7	14	58
	corresponding				
	samples				
	R1	R1≤3	3 <r1≤10< td=""><td>10<r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<></td></r1≤10<>	10 <r1≤20< td=""><td>20<r1< td=""></r1<></td></r1≤20<>	20 <r1< td=""></r1<>
40000	MR(%) (average/max)	-/-	23.8/23.9	21.6/21.6	2.6/3.6
400°C	Number of	0	2	3	61
	corresponding samples				

The total number of samples varies depending on a heat treatment temperature.

Basically the same results were obtained in both cases where $Co_{70}Fe_{30}$, $Co_{90}Fe_{10}$, $Ni_{60}Fe_{40}$, sendust, $Fe_{50}Co_{25}Ni_{25}$, $Co_{70}Fe_{5}Si_{15}B_{10}$, or the like was used as the ferromagnetic layers in the form of a single-layer or a multi-layer and where a Al_2O_3 film formed with reactive evaporation, a AlN film formed with plasma reaction, and a film of TaO, TaN or AlN formed with natural oxidation or nitridation was used as the non-magnetic layer.

Basically the same results also were obtained from the magnetoresistive elements having the configurations as shown in FIGS. 4 to 11. For the element that included a plurality of junctions (tunnel junctions) due to the non-magnetic layer, the maximum R1 was used as R1 of the element. In these elements, CrMnPt (thickness: 20 to 30 nm), Tb₂₅Co₇₅ (10 to 20 nm), PtMn (20 to 30 nm), IrMn (10 to 30 nm), or PdPtMn (15 to 30 nm) was used as the antiferromagnetic layer, and Ru (thickness: 0.7 to 0.9 nm), Ir (0.3 to 0.5 nm), or Rh (0.4 to 0.9 nm) was used as the non-magnetic metal film.

Example 2

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Example 1 confirmed that the MR ratio changed with the composition of the magnetic layers in the vicinity of the non-magnetic layer. In this example, the relationship between the composition of the ferromagnetic layer and the MR ratio was measured by using magnetoresistive elements that were produced by the same methods of film forming and processing as those in Example 1.

The composition of the ferromagnetic layer was analyzed with Auger electron spectroscopy, SIMS, and XPS. As shown in FIGS. 12A to 12D, the composition was measured in the vicinity and in the middle of the layer. In the vicinity of the interface, the composition in the range of 2 nm from the interface was measured. In the middle of the layer, the composition in the range of 2 nm, which extended in the thickness direction with the middle included, was measured. "Composition 1" to "Composition 9" in FIGS. 12A to 12D correspond to the items in each table below. The configurations of the elements in FIGS. 12A to 12D also correspond to the element types of a) to d) in each table.

An Al₂O₃ film (thickness: 1.0 to 2 nm) was used as the non-magnetic layer. The Al₂O₃ film was produced by forming an Al film with ICP magnetron sputtering and oxidizing the Al film in a chamber filled with a

mixed gas of pure oxygen and high purity Ar. A Ru film (0.7 to 0.9 nm) was used as the non-magnetic metal layer, and PdPtMn (15 to 30 nm) was used as the antiferromagnetic layer.

In some magnetoresistive elements, the ferromagnetic layers were formed so that their compositions or composition ratios were changed in the thickness direction. This film formation was performed by adjusting an applied voltage to each of the targets.

Composition 6 NisoFezo NixoFezo NisoFezo NisoFezo Composition 5 NisoFe₂₀ NisoFezo NisoFezo NisoFezo Composition 4 (ConsFezs)ssaPto2 (ConsFezs)99.1Pto3 (CorsFezs)97Pt3 CorsFers (ConsFe2s)99.8Pto2 (CorsFe2s)99.1Ptos Composition 3 (ConsFezs)snPts ConsFezs (ConsFe2s)99.ePto2 Composition 2 (CorsFe2s)99.1Pta3 (ConsFezz)37Pts ConsFe2s (ConsFe2s)ss.aPto2 (CorsFezs) 99.1 Pto.3 Composition 1 (ConsFezz)snPts ConsFe2s 22.2 24.5 24.3 15.3 10.1 22.3 23.2 23.2 ₩ % 14.9 10.2 23.1 24.2 25.2 25.4 26.3 26.3 24.7 24.7 24 Heat treatment temperature (°C) rt. 260 300 350 400 Sample Element No. type . **.** . **व** æ æ 8 က

TABLE 4a)-1

Composition 6 NisoFezo NisoFezo NisoFezo NisoFe20 Composition 5 NisoFezo NisoFezo NisoFezo NisoFezo (ConsFe2s)ssPt15 Composition 4 (ConsFezs)nPtzs (ConsFezs)41Pts9 (ConsFezs)38Pte2 Composition 3 (ConsFe2s)&Pt15 (ConsFezs)nPtzs (CoreFe2s)41Ptse (ConsFe2s)sePte2 (CorsFe2s)&Pt1s Composition 2 (ConsFegs)11Pt28 (CorsFe2s)41Ptse (ConsFeas)38Pte2 Composition 1 (ConsFegs)&&Pt15 (ConsFees)11Pt29 (ConsFers)38Pte2 (CorsFe2s)41Ptse 20.5 20.2 12.5 17.8 15.3 19.4 ₩ % Sample Element No. type æ . **.** . æ æ ა ဗ 7 œ

TABLE 4a)-2

Composition 6 NisoFezo NisoFezo NisoFezo NisoFezo Composition 5 NisoFezo NisoFezo NisoFezo NieoFezo (NisaFea)ss2Pta13Pdan | (NisaFea)ss2Pta13Pdan | (NisaFea)ss2Pta13Pdan (NisoFe-a)99.7Pto2Pdo1 (NisoFe₄₀)s1Pt₂Pd₁ Composition 4 NisoFea (NisoFe4)99.1Pto.2Pdo.1 (NisoFeso)snPt2Pd1 Composition 3 NieoFe40 (NisoFe-a)99.1Pta2Pda1 (NisoFesp)snPt2Pd1 Composition 2 NicoFe40 (NicoFe 2) & Pto 13 Pdo on (NisoFesa)ss.1Pta2Pda1 (NisoFeso)s1Pt2Pd1 Composition 1 NisoFean 18.1 15.8 10.2 20.9 20.9 21.1 19.9 19.7 19.8 22.1 19.1 21.2 22.1 15.1 19.9 22.3 22.2 22.1 盈多 Fleat treatment temperature (°C) 260 300 400 400 400 350 400 400 400 400 400 350 260 rt Element type æ B æ æ Sample No. 6 2 Ξ 27

TABLE 4b)-1

Composition 6 NisoFezo NisoFezo NisoFex NisoFezo Composition 5 NisoFezo NisoFezo NisoFe2o NisoFezo (NisoFeyo)11Pt19Pd10 (NicoFe-20)41Pt39Pd20 (NisoFe-a)8sPt10Pds (NisoFead)38Pt41Pd21 Composition 4 (NicoFe-co)71Pt19Pd10 (NisoFe-co)41Pt39Pd20 (NisoFe-20)85Pt 10Pds (NisoFe40)38Pt41Pd21 Composition 3 (NisoFeso)11Pt19Pd10 (NisoFe4)41Pt39Pd20 (NisoFe40)85Pt10Pds (NisoFe42)38Pt41Pd21 Composition 2 (NisoFe-so)nPt19Pd10 (NieoFea)41PtssPdzo (NisoFe-a)ssPt1aPds (NisoFe40)38Pt41Pd21 Composition 1 18.8 19.9 19.8 19.8 28.8 28.8 19.8 19.8 20.1 20.1 18.7 18.7 18.7 18.8 19.9 #3 16.8 15.9 12.3 9.8 19.1 Heat treatment temperature (°C) 300 300 400 350 260 300 400 r.t. 3300 350 400 400 400 400 Element type æ æ B <u>a</u> Sample No. 13 14 15 91

(Co15Fe25)99.7Iro.15Pdo.01Rho.08 (Co15Fe25)99.81ro.1Pdo.05Rho.05 (Co15Fe25)97Ir1.5Pd0.15Rh0.15 Composition 3 CorsFe25 Composition 2 CosoFe10 CosoFe10 CosoFe10 CosoFe10 Composition 1 CosoFe10 CosoFe10 CosoFe10 CosoFe10 22.5 24.5 24.1 15.2 9.9 23.7 23.4 15.3 MR % 11.3 22.2 24.2 24.1 24.1 23.9 23.8 22.9 23.3 24.2 Heat treatment temperature (°C) Element type а⁾ **a** а⁾ а⁾ Sample No. 17 18 19 20

24

TABLE 4c)-1

(Co15Fe25)99.8Iro.1Pdo.05Rho.05 (CorsFe2s)99.1 Iro.15 Pdo.07 Rho.08 (CorsFe2s)97Ir1.sPd0.75Rh0.75 Composition 6 CorsFe2s (CorsFers) 98.7 Iro.15 Pdo.07 Rho.08 (CorsFe2s)39.81ro.1Pdo.05Rho.05 (Co15Fe25)97Ir1.6Pdo.15Rho.15 Composition 5 CorsFe26 (CorsFe25)99.7 Iro.15 Pdo.07Rho.08 (CoreFers)99.8 Iro.1 Pdo.05Rho.05 (Co15Fe2s) 97 Ir1.5 Pdo.16 Rho.15 Composition 4 ConsFers 22.5 24.5 15.2 21.8 15.3 11.3 23.9 23.8 20.6 22.9 23.3 24.2 23.4 22.2 24.2 24.1 24.5 % % 24.1 9.6 23.7 Heat treatment temperature (°C) 260 300 400 260 300 350 400 260 300 350 400 350 r.t. 260 r. it r.t. Element type . В а) **В** (а Sample No. 18 17 19 20

TABLE 4c)-2

(C015Fe25)41Ir29.5Pd14.1Rh14.8 (Co15Fe25)38Ir31Pd15.5Rh15.5 (Co15Fe25)11 Iri4.5 Pd1.2 Rh1.3 (CorsFe2s)8s1rr.sPd3.1Rh3.8 Composition 3 Composition 2 CosoFe 10 CosoFe10 . CosoFe 10 Co90Fe10 Composition 1 CosoFeto CosoFe10 CosoFe10 CosoFe10 20.1 19.7 19.7 15.1 10.2 Heat treatment temperature (°C) r.t. 300 350 400 Element type а) а₎ **a ∂** TABLE 4c)-3 Sample No. 21 22 23 24

(Co15Fe25)41 Ir29.5Pd14.7Rh14.8 (CorsFe2s)38Ir31Pd15.5Rh15.6 (CorsFe2s)ssIrr.sPd3.1Rh3.8 (Co15Fe25)11Ir14.5Pd7.2Rh7.3 Composition 5 (Co15Fe25)41Ir29.5Pd14.1Rh14.8 (CoreFe2s)85Irr.5Pd3.7Rh3.8 (Co15Fe25)11Ir14.6Pd1.2Rh1.3 (CorsFezs)38Ir31Pd15.5Rh15.5 Composition 4 21.4 22.6 20.5 26.8 27.3 25.2 20.4 22.2 15.3 20.2 $\mathbb{R}^{\mathbb{S}}$ 21.1 21.4 23.2 23.1 19.7 15.1 15.1 20.1 Heat treatment temperature (°C) r.t. 260 300 350 400 260 350 400 r.t. 260 300 350 r.t. 260 300 350 400 r.t. 400 Element type а) (B **в** TABLE 4c)-4 Sample No. 21, 22 23 24

(Co15Fe25)71 Ir14.5Pd1.2Rh1.3

(Co15Fe25)85Ir7.5Pd3.1Rh3.8

Composition 6

(Co15Fe25)41Ir29.5Pd14.1Rh14.8

(CorsFe2s)38Ir31Pd15.5Rh15.5

10.2

(CorsFezs)88.8Pto.2Mn10 (CorsFers)ss1Pto3Mn4 (CorsFers)so1Pto3Mn9 (CorsFe2s)948Pto2Mns (CorsFezs)331Ptz9Mn4 (CorsFezs)832Ptz8Mn8 (CorsFezs)ssMns (CorsFezs)soMn10 (ConsFe2s) seuPto2 (CorsFezs)99,7Pto3 Composition 6 (ConsFezs)31Pt3 ConsFegs (ConsFezs)sesPto3Mnos (ConsFezs)snsPto3Mn1s (CorsFers)ss.2Pt3Mnos (CorsFers)ss.4Pt3Mn18 (CorsFe2s)seaPto2Mn1 (ConsFezs)97.3Pto1Mn2 (CorsFers)39Mn1 (CorsFers)39Mn2 (ConsFers)ssuPto2 (CorsFe2s)s9.7Pto3 Composition 5 (ConsFezs)37Pt3 ConsFe2s (CorsFe2s)99.7Pto3 (ConsFezs)39.8Pto2 Composition 4 (ConsFezz)srPts ConsFezs (CoreFezs)ss &Pto2 (CorsFe2s)99.1Ptas Composition 3 (ConsFeaslanPta CorsFe2s Composition 2 NisoFezo NisoFezo NisoFezo NisoFezo Composition 1 NisoFezo NisoFezo NisoFezo NisoFezo 33.8 35.5 18.9 34.2 14.8 21.8 35.5 32.2 33.3 34.4 35 34.9 20.6 ¥3 36.1 22.2 15.1 22.2 34.1 35.7 Heat treatment temperature (°C) 260 350 400 350 40 350 260 Lt. Element type <u>.</u> 3 7 Sample No. . 27 25 56 82

TABLE 4d)-1

(CorsFers)833Pt141Mn2 (CorsFers)818Pt144Mn4 (CorsFers) 402Pts18Mn2 (CorsFers)394Pts68Mn4 (CorsFess)37.2PteosMn2 (CorsFess)38.5PteosMn4 (CorsFers)89 ePtra 4Mn2 (CorsFers)88 2Ptra eMn4 (ConsFe2s)&Pt15 Composition 6 (CorsFers)11Ptza (ConsFe2s)41Ptse (ConsFers)34Pte2 (CorsFess)10sPt283Mnas (CorsFess)103Pt281Mn1 (CorsFezs) wePtsenMnas (CorsFezs) wePtse4Mn1 (CorsFezs)37.ePte1.1Mnas (CorsFezs)37.ePte1.4Mn1 (CorsFess)sasPtiasMnos (CorsFess)sasPtiasMni (ConsFe2s)&Pt15 (CorsFezs)41Pts9 (ConsFess)38Pte2 (ConsFezs)71,Ptzs Composition 5 (ConsFe2s)asPt15 (ConsFeashnPtza (ConsFers)38Pte2 Composition 4 (ConsFezs)41Pts (CorsFezs)88Pt18 (ConsFers)11Ptza Composition 3 (ConsFezs)41Ptse (CorsFezs) 38Pte2 Composition 2 NisoFezo NisoFezo NisoFezo NisoFezo Composition 1 NisoFezo NisoFezo NixoFezo NixoFezo 33.5 35.1 33.8 34.9 15.3 29.5 16.8 14.6 12.1 36.5 33.2 30.2 12.4 41.1 31.1 £38 temperature (°C) Heat treatment 400 350 rt. r.t. 3300 350 400 400 400 \$ 320 SS 1.t Element type · 23 · 🛪 3 B TABLE 40-2 Sample No. 23 ജ 31 32

The samples 1 to 8 in Table 4a) indicate that the addition of 0.3 to 60 at% Pt improves the MR characteristics after heat treatment at 300°C or more as compared with the sample that does not include Pt. In particular, the MR characteristics after heat treatment at 300°C or more tend to be improved by adding Pt in an amount of about 3 to 30 at%. The same tendency can be confirmed in each of the cases where $Co_{75}Fe_{25}$ in Table 4a) is replaced by $Co_{90}Fe_{10}$, $Co_{50}Fe_{50}$, $Ni_{60}Fe_{40}$ or $Fe_{50}Co_{25}Ni_{25}$, where $Ni_{80}Fe_{20}$ is replaced by sendust or $Co_{90}Fe_{10}$, and where Pt is replaced by Re, Ru, Os, Rh, Ir, Pd or Au.

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10

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The samples 9 to 16 in Table 4b) indicate that the addition of Pt and Pd with a ratio of 2:1 in a total amount of 0.3 to 60 at%, particularly 3 to 30 at%, improves the MR characteristics after heat treatment at 300°C or more as compared with the sample that does not include Pt and Pd.

The same tendency can be obtained when the ratio of the elements added is changed from 2:1 to 10:1, 6:1, 3:1, 1:1, 1:2, 1:3, 1:6, or 1:10. Moreover, the same tendency can be obtained by replacing Pt of (Pt, Pd) with Tc, Re, Ru, Rh, Cu or Ag and replacing Pd with Os, Ir or Au, i.e., a total of 28 combinations of the elements including (Pt, Pd). Further, the same tendency can be obtained in both cases where $Ni_{60}Fe_{40}$ is replaced by $Co_{75}Fe_{25}$ or $Fe_{50}Co_{25}Ni_{25}$ and where $Ni_{80}Fe_{20}$ is replaced by sendust or $Co_{90}Fe_{10}$.

The samples 17 to 24 in Table 4c) indicate that the addition of Ir, Pd and Rh with a ratio of 2:1:1 also improves the MR characteristics, like Tables 4a) and 4b). The same tendency can be confirmed when Ir is set to 1 and the contents of Pd and Rh are each changed in the range of 0.01 to 100. Moreover, the same tendency can be obtained in both cases where $Co_{90}Fe_{10}$ is replaced by $Ni_{80}Fe_{20}$, $Ni_{65}Fe_{25}Co_{10}$ or $Co_{60}Fe_{20}Ni_{20}$ and where $Co_{75}Fe_{25}$ is replaced by $Co_{50}Fe_{50}$, $Fe_{60}Ni_{40}$ or $Fe_{50}Ni_{50}$.

Further, the same tendency can be obtained by using the following combinations of the elements instead of (Ir, Pd, Rh): (Tc, Re, Ag), (Ru, Os, Ir), (Rh, Ir, Pt), (Pd, Pt, Cu), (Cu, Ag, Au), (Re, Ru, Os), (Ru, Rh, Pd), (Ir, Pt, Cu), and (Re, Ir, Ag).

The samples 25 to 32 in Table 4d) have the same tendency as that in Tables 4a) to 4c). Some samples show that Mn is diffused from the antiferromagnetic layer after heat treatment. However, the Mn diffusion can be suppressed by adding Pt. This indicates that the addition of Pt makes it possible to control the concentration of Mn at the interfaces of the

non-magnetic layer. The same tendency can be obtained by replacing Pt with Tc, Ru, Os, Rh, Ir, Pd, Cu or Ag. Moreover, the same tendency can be obtained by modifying the ferromagnetic layers to the above compositions.

(ConsFersbaMns (ConsFersbaMn10 (CorsFe2s)soMn10 (ConsFers)soMn10 (CorsFezs)ssMns Composition 6 (ConsFe2s) 95Mns (ConsFezs)seMns (CorsFers)solMn10 CorsFe2s ConsFe25 CorsFe2s ConsFe2s (ConsFers) sea Recus Mnos (ConsFers) seas Recus Mnus (CorsFers)981Re01Mn09 (Corst ezs) 91 sRea 15 Mina 1 (ConsFezsler, ReusMn.4 (Corsf ezs)99,85Re0.15 (CorsFezs)seMn1 (CorsFezs)seMn2 (ConsFe2s)38.5Re1.5 (ConsFers)99.9Reo.1 Composition 5 CorsFe2s (ConsFers)99.8Reo.2 (CoreFezs)99.1Re03 Composition 4 (ConsFezs)97Re3 ConsFezs (СозоГето)зя ВСео2 (CosoFe10)39.26Re0.15 (CosoFe10)39.7Re0.3 Composition 3 (CosoFe1a)srRes CosoFe10 (СозоFета)эээ Rea (СозоГето)за в Reт.5 Composition 2 CosoFe10 Composition 1 CosoFe10 CosoFe10 СозоРе10 CosoFe10 23.5 22.9 34.1 34.3 10.4 21.9 33.6 34.5 35.1 22.8 23.4 34.3 34.7 33.6 20.5 32.7 35.2 35.3 35.3 **E S** Heat treatment temperature (°C) 400 350 and 400 and 40 260 300 400 rt. 3300 350 400 400 400 400 Element type P 3 3 Sample ġ 33 34 35 8

TABLE 5a)-1

(CorsFers)ssMns (CorsFers)soMn10 (CorsFersbaMns (CorsFersbaMn10 (CorsFe2s)soMn10 (ConsFegs)soMn10 Composition 6 (CorsFe2s)9sMns (ConsFe2s)9sMns ConsFe2s ConsFezs CorsFe2s CorsFezs (ConsFers)es,1Re144Mnos (ConsFers)ea6Re144Mn1 (CorsFezsbarResoaMnos (CorsFezsbasResorMni (CorsFers) 101 Ress 4 Mnos (CorsFers) 68 8 Ress 2 Mn1 (CorsFezs)szRer.sMnos (CorsFezs)s1.6Rer.«Mn1 (CorsFe2s)85.5Re145 (CorsFe2s)n.sRe23.5 (CorsFezs)szsRers Composition 5 (ConsFezs)69Re31 (CorsFezs)&Re15 Composition 4 (ConsFers)11Regs (ConsFers)41Ress (ConsFe2s)38Res2 (CosoFe1a)&Re15 (CosoFeigesReiss (CosoFeigniRess (CosoFe10)41Ress (CosoFe10)seRes2 Composition 3 (CosoFe10)ncsRezes (CosoFe10)szsRe7.5 Composition 2 (CosoFe1a)69Re31 Composition 1 CosoFe10 СозоРе10 CosoFe10 СозоРе10 34.3 33.4 35.3 37.6 22.4 32.9 32.6 32.5 35.1 35.1 31.2 13.8 24.9 26.2 15.4 黑器 18.3 Heat treatment temperature (°C) 400 350 260 400 350 # 98 88 88 FF # 350 350 St Element type Œ Œ 3 Ê Sample Ž 37 88 33 8

TABLE 5a)-2

TABLE 5b)-1

					-				
Sample	Element		MR.	:	:	:			
S	No. type	temperature (°C)	(%)	Composition 1	Composition 2	Composition 3	Composition 4	Composition 5	Composition 6
		rt.	18						
_		260	37.8						
41	ં	300	40.3	NixoFezo	NisoFezo	NieoFe40	NisoFea	Confess	ප
		350	24.6						
		400	12.2						
		rt.	16.8						
		260	36.5					(CoruFeaol99.8Oso2	Coss &O So 2
42	ં	300	37.7	NisoFezo	(NisoFezo)sesRua	(NisoFe-a)99.8Ruo2	(NieoFe4o)99.8Oso.2		
		350	25.4					(CoroFex) 99Oso 2Mnos	Coss 8Oso2Mn4
		400	12.9					(Confeso)seOso2Mn1.8	Coso &Oso zMns
		r.t.	16.5		•				
		260	36.4					(Conaffeao)ss. 1Osos	Coss.1050.3
43	ં	300	38.1	NisoFezo	(NisoFezo)99.85Ruo.15	(NisoFe40)99.1Ruos	(NisoFean)ss.7Oso3		
		350	35.9					(ConFeso)sssOsosiMnos	Coss 10 So 3 Mn4
	•	400	30.5					(CoroFexolorsOsosMn.s	Coso 10 So 3 Mins
		r.t.	16.3						
		260	35.1					(CoroFeads1Oss	Cos10sa
4	િ	300	35.9	NisoFezo	(NisoFezo)sasRu1.5	(NisoFe4o)91Rus	(NieoFeao)370s3		
		350	38.2					(ConoFesolses)OssiMnon	Coss3Os29Mn36
		400	37.9	1				(Coroffesolss 4Os29Mn1.1	Coss 5Osz 1Mng 8

TABLE 5b)-2

Sample No.	Sample Element No. type	Heat treatment temperature (°C)	MR (%)	Composition 1	Composition 2	Composition 3	Composition 4	Composition 5	Composition 6
		rt.	15.5						
		260	30.6					(CondFeaglasOs1s .	CossOs15
45	ા	300	32.3	NisoFezo	(NisoFezo)sz.sRu7.s	(NisoFe40)85R1115	(NisoFe4a)86Os16		
		350	35.4					(ConoFessoleseOs149Mnos	C081.9OS145Mn3.6
		400	38.3					(ConoFessolss 9OS148IMn1.3	Con.9Os13.1Mn84
		rt.	17.6						
		260	32					(ConaFesa)nOssa	ConOsa
46	ા	300	33.1	NisoFezo	(NisoFezo)sasRu145	(NisoFe40)11Ru29	(NisoFeat)710szs		
		350	34.3					(Conolieso)nosOszasMnos	Coes.4OszeMn3.6
		400	35.1			-		(ConsFess)no1OszasMn1.3	CoesOsæeMne4
		rt.	11.7						
		260	30.3				,	(ConaFesso)41Osse	Co ₄₁ Oss
47	ા	300	32.4	NisoFezo	(NisoFezo)nosRuzos	(NisoFe-20)41Ru59	(NisoFeso)41Ossa		
		320	32.2					(ConoFess) 40.8Osss.1Mno.s	Coss.sOssasMnsa
		400	30.8					(ConoFessolvosOssa2Mn1.3	Co37,6OssaMine 4
		r.t.	9.5						
		260	15.2					(ConnFead)asOss2	CoseOse2
48	િ	300	18.1	NisoFezo	(NisoFezolesRusı	(NievFe40)38Rue2	(NisoFe40)38Ose2		
		350	15.6					(ConeFess)37,8Ose1,7Mno.5	Cose & Osse al Mrus e
		400	11.7					(CoroFesolsn.sOser.gMn.s	CosasOssasMns.4

(ConsFess)snaPto is Cuo is Minos (ConsFess)snaPto is Cuo is Minas (ConsFess)snaPto is Cuo is Minas (ConsFess)sna Pto is Cuo is Minas (CorsFers)s48Pto.1Cuo.1Mns (CorsFers)sePto.1Cuo.1Mnso (ConsFers)22.5Pt.1.5Cu1.4Mn46 (ConsFers)28.1Pt1.4Cu1.3Mn9.2 (CorsFe2s)99.7Pto.15Cuo.15 (CorsFezs)ss.ePto.1Cuo.1 (ConsFe2s)97Pt1.5Cu1.5 (CorsFezs)ssMns (CorsFezs)soMn10 Composition 6 CosoFe 10 (CorsFezs)se2Pt1sCu1sMn08 (CorsFezs)se4Pt1sCu1sMn18 (ConsFess)sasPto1Cuo1Mn1 (ConsFess)snsPto1Cuo1Mn2 (CorsFe2s)99.7Pto.15Cuo.15 (ConsFers) 99. Pto 1 Cuo 1 (CorsFezs)37Pt1.5Cu1.5 Composition 5 (CorsFe2s)seMn2 (CorsFezs)seMn1 ConsFe2s (ConsFezs)99.7Pta15Cua15 (ConsFezz)39.8Pto.1Cuo. (Constrezs)37Pt1.5Cu1.5 Composition 4 ConsFezs Composition 3 CosoFero СозоГето CosoFero CosoFe Composition 2 CosoFero СозоFело CosoFero CosoFe10 Composition 1 СозоРего СозоFело CosoFe10 CosoFe10 21.7 36.3 38.1 24.5 11.6 22.2 35.4 36.8 22.3 13.2 21.9 35.1 36.6 35.4 33.8 20.2 32.8 35.3 37.7 38.1 ES treatment temperature (°C) 400 350 SG ct 260 300 400 400 850 as the # 18 8 8 8 E 8 Sample Element
No. type type િ ા ં ા 49 ය 22 51

36

TABLE 5c)-1

(CorsFe2s)81.6Ptr2Cur2Mn4 (CorsFezs)38.4Pt28.6Ouze.aMn4 (CorsFezs)38Pt28.6Ouze.sMn8 (ConsFezs)ea2Pt139Cu139Mn4 (ConsFersles Pt.13.3Cu13.3Mne (CorsFezs)882Pt139Cu139Mn4 (ConsFers)31.1Ptz1.2Cu21.1Mns (Constress) 18 2 Pte 9 Cue 9 Mns (CorsFe2s)11Pt145Cu145 (CorsFers)41 PtrasCuras (CorsFezs)&Pt1.5Cu1.5 (CorsFers)3aPt31Ou31 Composition 6 (ConsFers)no1Pt144CU144Mnos (ConsFers)no2Pt144CU144Mn1 (ConsFers)40aPt29.4Cu293Mnos (CorsFers)318Pts08Cus08Mn08 (CorsFers)316Pts01Cus01Mn1 (CorsFess) sesPtrsCursMnos (ConsFers) sosPtra 2 Cura 2 Mn 1 (CorsFess)sa2Ptr.4Cur.4Mn1 (ConsFers)71Pt145Cu145 (ConsFe2s)41Pt28.5Cu28.5 (CorsFe2s)asDtr.sCur.s (ConsFezs)38Pt31 Cu31 Composition 5 (ConsFers)nPt145Cu145 (ConsFezs)41Pt225Cu235 (ConsFezs)ssPtnsCuns (ConsFezs)3ePt31Cu31 Composition 4 Composition 3 СозоРего CosoFe10 CosoFero СозоFето Composition 2 СозоFето СозоРе10 CosoFero CosoFe10 Composition 1 CosoFe10 СозоFето CosoFe10 $CosoFe_{10}$ 31.6 38.9 41.3 15.8 31.2 36.8 15.4 32.6 14.9 35.1 33.8 24.9 **E S** 32.7 24.7 31 treatment temperature (°C) Heat 400 350 and 400 and 40 400 350 T.t. 400 3300 Tr. 400 3300 4 Element type ા િ ા િ Sample No. 23 \$ 22 B

(CorsFers)ssMns (CorsFers)soMn10 (CorsFezs)seMns (CorsFezs)soMn10 (CorsFers)ssMns (CorsFers)soMn10 (ConsFers)seMns (ConsFers)seMn10 Composition 6 ConsFe2s ConsFers CorsFe2s ConsFe2s (ConsFersbamni (ConsFersbamni (CorsFezs)ssMn1 (CorsFezs)ssMn2 (CorsFezs)39Mn1 (CorsFezs)39Mn2 (CorsFezs)ssMn1 (CorsFezs)ssMn2 Composition 5 ConsFe2s ConsFe2s CorsFe2s CorsFe25 Fees 68 Ptos Mno.15 Composition 4 FessePto2Mno2 Fese PtsMno FessaMno2 FessaPto2 Fee: 1Ptos FenPts Fe Composition 3 Feg.7Pto3 FessaPta2 Fe97Pt3 Ę. Composition 2 NisoFezo NisoFezo NisoFezo NisoFezo Composition 1 NisoFezo NisoFe20 NisoFezo NisoFezo 15.4 12.5 27.1 28.4 29.3 18.9 29.7 19.3 29.4 27.2 29 12.3 26.5 26.8 28.7 28.2 15.1 ₹8 8 9 Heat treatment temperature (°C) 400 350 360 rt 400 350 rt 4 35 36 Ft 40 350 260 rt Sample Element No. type type જ ા ા િ 21 쫎 23 8

TABLE 5d)-1

(ConsFers)ssMns (ConsFers)soMn10 (CorsFezs)ssMns (CorsFezs)soMn10 (CorsFezs)95Mns (CorsFezs)90Mn10 (CorsFers)ssMns (CorsFers)soMn10 Composition 6 ConsFe2s CorsFe2s CorsFe2s CorsFe2s (CorsFezs)seMn1 (CorsFezs)seMn2 (CorsFers)seMn1 (CorsFers)seMn2 (CorsFers)seMn1 (CorsFers)seMn2 (CorsFezs)99Mn1 (CorsFezs)98Mn2 Composition 5 CorsFe2s CorsFe2s Consfiers ConsFezs Composition 4 FegePt15 FenPtz Fe41Pts9 FessPts2 Composition 3 FessPt16 FenPtz Fe41Pts Fe38Pte2 Composition 2 NisoFezo NisoFezo NisoFezo NisoFezo Composition 1 NisoFezo NisoFezo NisoFezo NisoFezo 27.8 29.1 33.4 23.9 24.9 30.4 25.1 27.4 29.4 10.3 18.5 **E S** 22.1 33 Heat treatment temperature (°C) 400 350 J.t. 260 260 300 350 400 400 400 Sample Element No. type type ા ં ા ગ 61 62 \mathfrak{S} 2

TABLE 5d)-2

(ConsFers)948Mns2 (ConsFers)888Mn102 (CorsFezs) tes al Mn102 (ConsFess)ss aMn 102 (ConsFezs)948Mns.2 (ConsFers)suaMns2 (CorsFezs)99.aMno2 (CorsFess)948Mns.2 (CorsFe2s)99.aMno.2 (CorsFe2s)88.8Mn102 (CorsFe2s) 99.8 Mno.2 (ConsFezs) 99.8 Mino.2 Composition 6 (CorsFezs)988Mn1.2 (CorsFezs)918Mn22 (CorsFezs)sssMn1.2 (CorsFezs)srsMn2.2 (ConsFers)38.8Mn1.2 (CorsFe2s)ssaMno2 (CorsFe2s)99.kMno2 (CorsFe2s)388Mn1.2 (CorsFezs)91.8Mn22 (CorsFe2s)91.aMn22 (ConsFess) 99. gMno.z (ConsFers)99,8Mno.2 Composition 5 FegsePtosMnoss Composition 4 Fees. Proz Mno. FeesePto2Mno2 Fess.sPto3Mno2 Fese Ptz sMnos FeerPtz.eMna2 Fess Mno.2 FesseMno4 Composition 3 FessePto2Mno2 Fess.sPto3Mno2 FearPtzeMnoz Feesel Mno2 (NisoFeso) Minoz (NisoFeso) Minoz (NisoFezo)ss.sMno2 (NisoFezo)ss.sMno2 (NisoFezo)ssaMnaz Composition 2 (NisoFezo) 93.8 Mino.2 (NisoFezo)se.aMno2 (NisoFezo)39.8Mno2 Composition 1 12.6 28.5 29.1 18.9 12.8 28.4 29.1 19.5 15.6 27.4 30.1 33.4 12.5 33.6 36.7 £3 15.1 12.7 temperature .(°C) Heat treatment 400 350 Sp. rt 4 30 80 80 H 260 300 400 300 260 400 350 Sample | Element type ા િ ા ા TABLE 6a)-1 ż 8 8 88 63

. (CorsFe2s)948Mn52 (CorsFe2s)888Mn102 (CorsFers)sesMns2 (CorsFers)sesMn102 (CorsFers)sasMns2 (CorsFers)ssaMn102 (CorsFe25)888Mn102 (ConsFezs)seaMns2 (CorsFe2s) 99.4 Mna2 (ConsFe2s)99.8Mn0.2 (CorsFe2s) seMno2 (ConsFersbergMno2 Composition 6 (CorsFe2s)seaMn1.2 (CorsFezs)ssaMn12 (CorsFezs)s18Mn22 (CorsFe2s)99.aMn0.2 (ConsFe2s)seaMn1.2 (CorsFe2s)91.8Mn22 (CorsFe2s)#8Mna2 (CorsFe2s)97.8Mn2.2 (CorsFezs)99.aMno.2 (CorsFers)sasMn1.2 (CorsFe2s)91.eMn22 (CorsFe2s) 99 MMno.2 Composition 5 Composition 4 FessPt148Mno2 Fe11Pt288Mn02 Fe41PtsasMno2 FesePter.eMno.2 Composition 3 FessPt148Mno2 Fe11PtzasMno2 Fe4 Ptsa Mno2 FesePtersMno2 (NisoFezo)99.8Mno.2 (NisoFezo)99.8Mno2 (NisoFezo)ss.sMno.2 (NisoFezo)99.elMno2 Composition 2 (NisoFezolssaMno2 (NisoFezo) se aMnoz (NisoFezo)ss.alMno.2 (NisoFezolss.aMno. Composition 1 25.3 29.9 34.2 39.6 25.3 37.9 34.2 **E S** 20.5 22.3 25.1 27.1 18.7 (°C) r.t. 260 300 350 400 Heat treatment 260 260 300 350 400 400 400 400 400 400 40 350 260 40 350 350 type . Element િ ા ા ા Sample ż 63 20 7 $\frac{1}{2}$

(ConsFers)susMnas (ConsFers)sesMn104 (CorsFezs)sasMnss (CorsFezs)sssMn104 (CorsFess) was Minisa (CorsFess) was Minisa (CorsFe2s)99.5Mn0.5 (CorsFezs) se sMnos (CorsFe2s)99.sMn0.s (CorsFe2s) ses Mns.s (ConsFe2s)89.6Mn10.4 (CorsFe2s) 99.5 Mno.5 Composition 6 (CorsFezs)sssMn1.5 (CorsFezs)91.5Mn2.5 (CorsFezs)ss sMn1.5 (CorsFezs)s7.5Mn2.5 (CorsFers)ss.sMn1.s (CorsFers)97.sMn2.s (CorsFezs)sasMn1.s (CorsFezs)s1.sMn2.s (CorsFe2s)s9.sMn0.s (CorsFezs) 99.s Mnos (CorsFe2s) 99.5 Mno.5 (CorsFe2s) 99.5 Mino.5 Composition 5 Composition 4 Fess Pro2Mno. FesessPt2sMnoes FegaPtazMnos Fess 2 Ptos Mnos FearPt2.sMno.s FeeePto3Mno7 Fess.sMno.s Fegs Mno. Composition 3 FessaPtozMnos Fess.2Pto.3Mno.s Fe31Pt2.5Mnas Fees.sMnos (NisoFezo)sesMnos (NisoFezo)99.5Mnois (NisoFezo)sesMnos (NisoFezo)se, eMnos Composition 2 (NisuFezo)99.sMnos (NisoFezo)sseMnas (NisoFezu) 99.5 Mno.5 (NisoFezo)sesMnas Composition 1 12.8 28.6 28.9 19.5 15.6 28.6 29.5 12.4 29.9 28.4 27.6 29.4 34.4 37.7 12.7 30.8 12.8 15.7 ES 27.1 temperature (°C) Heat treatment 400 350 and 400 and 40 40 350 26 Lt \$ 320 38 Lt r.t. 260 9330 Element type ા ા ગ ા TABLE 6b)-1 Sample ġ 73 35 76 74

(ConsFers)sasMnss (ConsFers)sasMn104 (CorsFers)sasMnss (CorsFers)sseMn104 (ConsFezs)945Mn55 (CorsFe2s) 99.sMno.s (ConsFers)sqsMnss (CorsFe2s) 88.8 Mn 10.4 (CorsFers) 99.5 Minos (CorsFe2s)99.sMno.s (ConsFe2s)eseMn10.4 (CorsFezs)99.sMnos Composition 6 (ConsFezs)sasMn1.5 (ConsFezs)97.5Mn2.5 (ConsFers) 98 sMn1.5 (ConsFers) 91 sMn2 s (ConsFezs)sssMn1.5 (ConsFezs)91.5Mn2.5 (CorsFe2s)99.sMnos (CorsFe2s)38.3Mn1.5 (CorsFe2s) 99.5 Mno.5 (CorsFe2s)ss.sMno.s (CorsFers)91.sMn2.s (ConsFezs)99.sMnos Composition 5 Fева9Pt₁₄5Mnos Composition 4 FesePt₁₄sMnos Fe₇₁Ptza.sMno.s Fe41PtsasMnos Fe38Pte1.sMno.s Composition 3 Fe11PtzasMnos Fe41PtsasMnos FesePtersMnos FessPt145Mnas (NisoFezo)99.sMnas (NisoFezo)99.51Mnos (NisoFezo)ss.sMno.s (NisoFezo)99.5Mno.5 Composition 2 (NisoFezo)sseMnos (NisoFezo)ss.sMnas (NisoFezo)99.sMno.s (NisoFezo)39.sMno.s Composition 1 22.5 19.5 16.5 26.8 33.8 10.4 31.238.4 25.5 27.1 24.9 19.9 26.7 42.4 12.1 11.6 ₹3 13.1 42.1 စ္တ 33 Heat treatment temperature (°C) # 18 8 8 8 E 4 38 88 R # 18 8 8 8 4 35 36 rt Element type િ ા ા િ TABLE 6b)-2 Sample Š 23 8 4 82

(CorsFers)24 iMns9 (CorsFers)89 iMn109 (CorsFers)sa 1Mnss (CorsFers)sa 1Mn103 (CorsFers)241Mn59 (CorsFers)281Mn109 (CoreFees)941Mns9 (ConsFezs)es,1Mn109 (CorsFe2s)99Mn1 (CorsFezs)#Mn1 Composition 6 (CorsFe2s)mMn1 (ConsFezs)99Mn1 (CorsFers)saMnz (CorsFers)srMn3 (CorsFezs)ssMnz (CorsFezs)srMn3 (CorsFers)seMnz (CorsFers)snMns (CorsFers)saMn2 (CorsFers)srMn3 Composition 5 (CorsFe2s) Mn1 (ConsFezs)#9Mn1 (ConsFezs)seMn1 (CorsFezs)99Mn1 FessePt2Mn1.15 Composition 4 FessePta2Mn12 Fess.5PtasMn12 FessaPto2Mn1 Fesa, Ptos Mni FessaMn1.2 FestPt2Mn1 FessMnı Composition 3 FessaPto2Mn1 Fese 7 Ptos Mn1 FearPtaMnı FessMnı Composition 2 (NisoFezo)seMn1 (NisoFezo)ssMn1 (NisoFezo)ssMn1 (NisoFezolssMn1 Composition 1 (NisoFezo)ssMn1 (NisoFezolse)Mn1 (NisoFezo)ssMn1 (NisoFezo)seMn1 **E** 3 28.4 28.6 18.9 15.1 12.5 28.3 29.6 19.09 15.3 26.9 29.5 28.8 12.5 27.4 29.6 33.3 12.1 36.2 Heat treatment temperature (°C) 400 350 as t 400 350 Signature 1.1. 280 280 280 280 280 400 400 400 Sample Element No. type ગ ં ગ િ TABLE 6c)-1 82 83 8 8

(CorsFezs)24 1Mns.9 (CorsFezs)28 1Mn109 (CorsFers)ea i Mnas (CorsFers)es i Mnios (CorsFezs)841Mns9 (CorsFezs)881Mn109 (CorsFers)941Mns9 (CorsFers)891Mn109 (CoraFe2s)seMn1 Composition 6 (CorsFezs)39Min1 (ConsFeas)seMni (ConsFe2s)seMn1 (CorsFezs)ssMn2 (CorsFezs)srMn3 (CorsFe2s)ssMn2 (CorsFe2s)srMn3 (ConsFers)saMnz (ConsFers)snMn3 (CorsFezs)seMnz (CorsFezs)srMns Composition 5 (CorsFe2s)99Mn1 (ConsFers)ssMn1 (ConsFers)seMn1 (CorsFe2s)ssMn1 Composition 4 FeesePt14Mn1.1 FessPt₁₄Mn₁ FenPtaMnı Fe41PtssMn1 FessPtaiMni Composition 3 FenPtzsMn1 FessPt14Mn1 Fe41PtssMn1 FesePte1Mn1 (NisoFezo)seMn1 Composition 2 (NisoFezo)ssMn1 (NisoFezo)ssMn1 (NisoFezo)ssMn1 (NisoFezo)ssMn1 (NisoFezo)ssMn1 (NisoFezo)ssMn1 (NisoFezo)ssMn1 Composition 1 26.8 31.5 13.343.8 25.6 26.9 34.8 19.8 22.6 19.7 16.6 ₹3 42.4 39.4 12.1 89 25.1 27 37 Heat treatment temperature (°C) 260 350 at t. 40 350 Sch 4 350 260 rt 260 300 400 Element, type ા ા ા ૦ Sample No. 82 8 87 88

(CorsFess)33.1Mnes (CorsFess)88.2Mn1.8 (CorsFezs)83.1Mn89 (CorsFezs)882Mn118 (CorsFers)33.1Mne9 (CorsFers)882Mn118 (ConsFezs)83.1Mne9 (ConsFezs)88.2Mn11.8 Composition 6 (CorsFezs)seMn2 (CorsFe2s)seMn2 (ConsFers)seMn2 (ConsFezs)saMn2 (CorsFers)srMns (CorsFers)seMn4 (CorsFezs)37Mn3 (CorsFezs)38Mn4 (CorsFezs)srMns (CorsFezs)seMn4 (CorsFers)31Mn3 (CorsFers)38Mn4 (CorsFe2s)seMn2 (CorsFe2s)seMn2 Composition 5 (CorsFezs)seMn2 (ConsFers)ssMn2 FearsePto3Mn215 Composition 4 Fesr.ePto.zMnz FegrePto2Mn22 Feer, Pta3Mn2 FessaPtaMn21 FegraMn22 · FesePt2Mn2 FeseMn₂ Composition 3 FessaPto2Mn2 Fe91.1Pto.3Mn2 FesePtsMns FessMn₂ Composition 2 (NisoFezo)s«Mn2 (NisoFezo)ssMn2 (NisoFezo)ssMn2 (NisoFezo)seMn2 (NisoFezo)seMnz (NisoFezo)seMn2 (NisoFezo)seMn2 Composition 1 (NisoFezo)seMn2 28.1 28.3 12.5 28.2 14.9 12.4 18.9 11.9 ₹3 26.6 29.1 28.4 30.2 32.9 35.8 15.1 27.7 21 Heat treatment temperature (°C) 260 350 350 350 400 400 400 400 400 400 40 30 30 Lt 40 350 360 rt Element type ઉ ં ত િ Sample Š 8 ೪ 91 83

TABLE 6d)-1

(CorsFees)89.1Mn8.9 (CorsFees)88.2Mn11.8 (ConsFess)88,1Mn69 (ConsFess)88,2Mn11,8 (CorsFe2s)88.2Mn11.8 (CorsFezs)ss 1Mnes (CorsFezs)88.2Mn11.8 (CorsFe2s)33.1Mne9 Composition 6 (ConsFe2s)seMn2 (CorsFe2s)seMn2 (CorsFe2s)ssMn2 (CorsFe2s)seMn2 (CorsFess)37Mn3 (CorsFess)38Mn4 (ConsFers)31Mn3 (ConsFers)38Mn4 (CorsFersbarMns (CorsFersbarMn4 (CorsFers)31Mn3 (CorsFers)36Mn4 Composition 5 (CorsFe2s)seMn2 (CorsFe2s)seMn2 (CorsFe2s)ssMn2 (CorsFe2s)saMn2 Composition 4 FessPt13Mn2 Fen.PtznMnz Fe41Pts1Mn2 FesePteoMn2 Composition 3 Fe38Pt60Mn2 FessPt13Mn2 Fe11Ptz1Mn2 Fe41Pts1Mn2 (NisoFezo)ssMn2 (NisoFezo)ssMnz (NisoFezo)seMn2 (NisoFezo)seMn2 Composition 2 (NisoFezo)ssMn2 (NisoFezo)seMn2 (NisoFezo)ssMn2 (NieoFezo)ssMn2 Composition 1 13.5 32.2 40.6 46.8 38.6 44.5 11.9 25.5 19.9 19.8 16.8 E S 12.4 25.7 28.1 27.1 10.4 27.1 42 37 temperature (°C) Heat treatment 49 350 36 rt 400 40 350 as t Element type ા ં જ ા Sample No. .8 83 94 32

(CorsFers)903Mn9.7 (CorsFers)86.5Mn145 (ConsFers)303Mn97 (ConsFers)865Mn145 (CorsFers)303Mn9.7 (CorsFers)88.5Mn145 (CorsFers)803Mn9.7 (CorsFers)805Mn145 (CorsFers)95Mns (CorsFezs)ssMns Composition 6 (ConsFezs)ssMns (CorsFezs)95Mns (CorsFezs)941Mns.9 (CorsFezs)931Mne9 (CorsFezs)94 1Mns.9 (CorsFezs)93 1Mns.9 (CorsFezs)sa1Mnss (CorsFezs)sa1Mnss (CorsFers)sa1Mnss (CorsFers)sa1Mnss (ConsFers)9sMns (ConsFers)ssMns Composition 5 (CorsFe2s)35Mns (CorsFezs)ssMns FesassPto3Mns.15 Composition 4 FestePto2Mns2 FestsPto2Mns Fese 1 Pto.3 Mns FessePtsMns. Festal Mns2 $Fe99Pt_2Mn_5$ FessMns Composition 3 Fesa 1 Pto 3 Mins FessePto2Mns FessPt₂Mns FessMns (NisoFezo)ssMns (NisoFezo)ssMns Composition 2 (NisoFeza)ssMns (NisoFezo)ssMns (NisoFezo)ssMns (NixoFezo)ssMns Composition 1 (NisoFezo)ssMins (NisoFezolssMns 12.4 28.3 28.4 18.5 14.8 12.228.9 14.9 28.8 27.9 12.4 27.1 29.9 31.6 32.8 11.8 26.4 **₹3** 18.7 83 Heat treatment temperature (°C) 260 300 400 400 400 350 Sept. 1. 260 260 300 400 400 400 400 400 400 Sample Element No. type ા ં િ િ 100 97 88 83

TABLE 7a)-1

(CorsFezs)2031Mn97 (CorsFezs)85.5Mn145 (CorsFezs)so3Mn97 (CorsFezs)ss3Mn145 (ConsFezs)es sMn145 (CorsFe2s)8s.sMn14s (CorsFe2s)sosMns.r (ConsFe2s)30.3Mn9.7 (CorsFezs)ssMns (CorsFezs)ssMns Composition 6 (ConsFe2s)ssMns (CorsFezs) saMns (CorsFers)sq1Mns9 (CorsFers)ss1Mns9 (CorsFers)941Mns9 (CorsFers)931Mns9 (CorsFezs)941Mns9 (CorsFezs)931Mne9 (CorsFers)sq1Mns9 (ConsFezs)ss 1Mnes (CorsFe2s)ssMns (CorsFezs)ssMns (CorsFe2s)ssMns (CorsFezs)9sMns Composition 5 Composition 4 FessPtioMns Fen.Pt24Mns Fe41Pts4Mns FeaePtsnMns Composition 3 FessPtioMns Fen.Pt24Mns Fe41Pts4Mns FeaePtsnMns (NisoFezo)ssMns (NisoFezo)ssMns Composition 2 (NisoFezo)ssMns (NisoFezo)ssMns (NisoFezo)ssMns (NizoFezo)ssMns (NisoFezo)ssMns (NisoFezo)ssMns Composition 1 31.8 45 12.2 25.8 27.9 36.7 25.3 26.9 26.9 34.4 40.5 19.9 22.2 19.5 16.5 13.3 43.2 10.3 11.7 **B B** 40.1 Heat treatment temperature (°C) Sample Element No. type 73 ા ા ા TABLE 7a)-2 104 102 103 101

(CorsFezs)81.9Mn12.1 (CorsFezs)83.1Mn18.3 (ConsFess) Ban Minies (CorsFezs)83.7Mn18.3 (CorsFe2s)83.1Mn18.3 . (ConsFezs)87.9Mn12.1 (ConsFers)ersMn121 (CorsFe2s)81.9Mn121 (CorsFe2s)s2Mns (CorsFezs)s2Mns (ConsFe2s)s2Mns Composition 6 (ConsFers)szMns (CorsFess)91.2Mna8 (CorsFess)903Mn9.7 (CorsFe2s)91.2Mna8 (CorsFe2s)903Mn97 (CorsFezs)sosMns.1 (CorsFe2s)91.2Mnaa (CorsFers)303Mn9.1 (CorsFezs)91.2Mn88 (CorsFe2s)s2Mna (CorsFe2s)s2Mns Composition 5 (CorsFe2s)s2Mns (CorsFezs)s2Mns Fe91.65Pto2Mn8.15 Composition 4 Feese-Pt2Mnacs FearePtosMna. Fear, Ptos Mna FearaPto2Mns Fe91.85Mn8.15 FesoPt2Mns FeezMns Composition 3 Fe91.8Pto2Mns Fear Ptos Mns FesoPtaMns FeezMins (NieoFezolezMns (NisoFezo)szMns (NisoFezo)szMns Composition 2 (NisoFezobszMns (NisoFezolezMns (NisoFezo)szMns (NisoFezo)szMns (NisoFezolszMns Composition 1 27.6 27.8 11.6 14.3 12.2 27.9 28.2 24.9 25.8 26.8 29.7 30 ES 18.1 28.1 Heat treatment temperature (°C) 260 300 400 40 350 361 rt 4 35 86 Ft \$ 38 88 B Sample Element No. type િ ા િ ં 105 90 107 108

TABLE 7b)-1

(CorsFezs)er.9Mn121 (CorsFezs)es.1Mn163 (CorsFezs)81.9Mn12.1 (CorsFezs)82.1Mn163 (CorsFers)anaMni21 (ConsFe2s) ten 1 Min 183 (CorsFe2s)83.1Mn16.3 (CorsFe2s)er.9Mn121 (CorsFezs)s2Mns (CorsFers)s2Mns Composition 6 (CorsFe2s)s2Mns (ConsFe2s)92Mna (CorsFers)91.2Mna8 (CorsFers)903Mn9.1 (CorsFezs)91 2Mnas (CorsFezs)903Mn97 (CorsFers)91.2Mn8.8 (CorsFers)91.2Mn88 (CorsFers)903Mn97 (CorsFe2s)so3Mn9.1 Composition 5 (CorsFezs)s2Mns (CorsFezs)92Mns (CorsFers)s2Mns (CorsFe25)s2Mna Composition 4 FessPts₄Mns FessPt1Mns Fen Ptzı Mns Fe41Pts1Mns Composition 3 FessPt₂Mns Fe71Pt21Mns Fe41Pts1Mns FesePts4Mns (NisoFezo)szMns Composition 2 (NisoFezo)s2Mns (NisoFezo)szMns (NisoFezo)s2Mns (NisoFezo)s2Mns (NisoFezo)92Mns Composition 1 (NisoFezo)s2Mns (NisoFezo)szMns 12.9 26.2 24.9 26.2 31.1 32.3 37.3 30.4 10.6 24.9 26.1 28.5 32.6 18.3 10.2 19.7 15.4 temperature (°C) Heat treatment 260 300 350 360 360 360 400 400 r.t. 300 350 400 Element type િ ં ા ં Sample Ś 100 110 Ξ 112

TABLE 7b)-2

(CorsFezs)845Mn155 (CorsFezs)81Mn19 (CorsFezs)ersMn155 (CorsFezs)81Mn19 (CoraFezs)&asMn185 (CoraFezs)81Mn19 (CorsFers)easMn1ss (CorsFers)e1Mn19 (ConsFe2s)&Mn12 (CorsFezs)æMn12 (CorsFe2s)#Mn12 (CorsFe2s)æMn12 Composition 6 (CorsFees)81.3Mn12.1 (CorsFees)866Mn13.4 (CorsFezs)813Mn127 (CorsFezs)888Mn134 (CorsFe2s)813Mn121 (CorsFe2s)869Mn134 (CorsFess)81.3Mn12.1 (CorsFess)866Mn13.4 (CorsFe2s)æMn12 (CorsFe2s)88Mn12 (ConsFe2s)88Mn12 (CorsFezs)æMn12 Composition 5 Fegres Ptos Mn1205 Composition 4 Fear Pto 2 Min 21 FesraPto2Mn12 Fear, Ptos Mn12 FesePt2Mn12 FegraMn121 FessMn12 Fевт. РъсозМица Composition 3 FearaPto2Mn12 FessPt2Mn12 FessMn12 (NisoFezo)selMn12 (NisoFezo)seMn12 (NisoFezo)seMn12 (NisoFezo)ssMn12 Composition 2 (NisoFezolæMn12 (NisoFezolssMn12 (NisoFezolssMn12 (NisoFezo)ssMn12 Composition 1 56.9 23.5 27.9 26.5 13.6 26.5 17.2 26.6 11.8 13.7 11.5 27.2 E B 26.1 25.7 13 24 temperature (°C) Heat treatment 400 350 ct. 400 350 at t 350 360 E 400 350 tr 홍 Element type િ ા ગ ા TABLE 7c)-1 Sample ż 113 114 115 116

TABLE 7c)-2

			_					_		_	_		,	_							
Composition 6	(ConsFers)seMn 12			(ConsFe2s)845Mn155	(CorsFe2s)81Mn19	(CorsFers)æMn12			(CorsFess)&sMn155	(CorsFe2s)81Mn19	(CorsFezs)agMn12			(CorsFers)easiMn155	(CorsFezs)81Mn19		(CorsFe2s)88Mn12		(ConsFezs)2413Mn155	(CorsFe25)81,Mn19	
Composition 5	(CorsFe2s)æMn12			(CorsFezs)873Mn127 (CorsFezs)886Mn134		(СолъБегь)ваМп12			(ConsFersbaraMn127 (ConsFersbaseMn134		(CorsFe2s)88Mn12			(CorsFezs)813Mn121 (CorsFezs)866Mn13.4		(CorsFezs)ssMn12			(ConsFe2s)87.3Mn12.1	(CorsFe2s)æ6Mn134	
Composition 4				Fen:PtnMn12					Fe41Pt41Mn12					FesePtsoMn12							
Composition 3		6			FenPenMinz					Fe41Pt41Mn12					FessPtcoMn12						
Composition 2	-			(NisoFesz)ssMn12					(Міва Рега)ваМіні г					(NisoFezo)ssMn12							
Composition 1				(NisoFezz)ssMn12					(NiseFeadseMn12					(NisoFesa)saMn12							
MR (%)	11.9	25.9	30.2	27.2	29.9	10.1	23.9	25.7	26.8	29.4	10.1	24.2	25.6	24.9	27.2	6.6	19.2	21.2	17	13.9	
Heat treatment temperature (°C)	r.t.	260	300	350	400	r.t.	260	300	350	400	rt.	260	300	350	400	rt.	260	300	350	400	
Sample Element No. type				જ					ô						ઉ						
Sample No.	Sample No.					118					119						120				

(CorsFe2s)15.1Mn23.9 (CorsFe2s)786Mn21.4 (CorsFees)18.1Mn239 (CorsFezs)786Mn21.4 (ConsFezs) 75.1 Mn 23.9 (CorsFe2s)186Mn21.4 (ConsFe2s)15.1Mnz39 (CorsFe2s) 18.6 Mn21.4 (CorsFe2s)81Mn19 (CorsFezs)81Mn19 (CorsFe2s)81Mn19 (CorsFe2s)a1Mn19 Composition 6 (CorsFe2s) 80 sMn 19 s (CorsFezs)80.sMn19.5 (CorsFezs)wsMn195 (CorsFe2s)80.sMn 19.5 (CorsFers)@Mnzo (CorsFe2s)81Mn19 (CorsFers)soMnzo (ConsFezs)a1Mn19 (CorsFezs)81Mn19 (CorsFezs)æMnæ (ConsFe2s)81Mn19 (CorsFezs)soMn20 Composition 5 FegrsPto2Mn1908 Composition 4 FesoaPto2Mn19 FegorPtosMn19 FegossMn1906 FensPtzMn19 FeatMn19 Composition 3 Feg. 7 Pto 3 Mn 19 FesosPtozMn19 FersPtsMn19 FeatMn19 (NisoFezolsı Minis (NisoFezolsı Mn19 (NisoFezola1Mn19 (NisoFezo)81Mn19 Composition 2 (NisoFezolsı Mrn 19 (NizoFezo)в1Мп19 (NisoFezo)sıMnıs (NisoFezolsı Mn19 Composition 1 21.8 10.9 24.2 25.3 16.1 12.8 25.5 26.9 27.2 22.7 23.1 ¥3 12.8 25.1 21.9 16.1 26.1 Heat treatment temperature (°C) 250 250 250 250 250 250 250 250 250 250 4 35 38 25 T \$ 13 S S S S Element type ા ં つ ા TABLE 7d)-1 Sample No. 121 122 123 124

(CorsFe2s)186Mn21.4 (CorsFe2s)15.1Mn29 (CorsFers) 186 Mn 21.4 (CorsFers) 151 Mn 239 (CorsFees)186Mn21.4 (CorsFees)151Mn29 (ConsFezs) 78 6 Mn 21.4 (CorsFe2s) 15.1 Mn239 (CorsFezs)81Mn19 (CorsFe2s)81Mn19 (CorsFers)81Mn19 (Соль Fe 25) в 1 Мп 19 Composition 6 (CorsFezs)205Mn195 (CorsFezs)20Mn20 (CorsFess)805Mn195 (CorsFess)80Mn20 (CorsFezs)80sMn19.5 (CorsFezs)80Mn20 (CorsFe2s)20.5Mn19.5 (CorsFezs)81Mn19 (CorsFe2s)81Mn19 (CorsFezs)81Mn19 (CorsFezs)81Mn19 (CorsFees)soMnzo Composition 5 Composition 4 Fer4Ptr/Mn19 Fen.Pt.oMn.19 Fe41Pt40Mn19 FessPt₄₃Mn₁₉ Composition 3 Fen4PtnMn19 FenPtioMnis Fe41Pt40Mn19 FeaePtaMn19 (Nімо Гегодзі Мін 19 (NisoFezolsı Mn19 (NisoFezo)sı Min 19 (NisoFezolsı Mn19 Composition 2 (NisoFezolsı Mrn19 (NisoFezolsı Mn19 (NisoFezola:)Mn19 (NisoFezo)sı Mn19 Composition 1 . 8 25.8 24.4 9.9 22.1 24.2 23.1 9.8 24.2 18.2 20.1 9.5 15.1 24 temperature (°C) Heat treatment 300 sec 400 350 as 400 350 cm 40 350 360 rt Element type ં ಾ ં િ Sample ġ 125 126 127 128

TABLE 7d)-2

(CorsFess)16.4Mnzs 6 (CorsFess)149Mnzs.1 (CorsFe2s) 18.4 Mn238 (CorsFers)749Mn251 (CorsFees)16.4Mnza6 (CorsFers) 18.4 Mn23.6 (CorsFezs)raMnzz (CorsFe2s)18Mn22 (CorsFezs)18Mn22 (CorsFezs)149Mn251 (CorsFe2s)149Mn25.1 (CorsFe2s)raMn22 Composition 6 (CorsFers)111Mnr23 (CorsFers)114Mnr26 (CorsFess)71.1Mn223 (CorsFess)71.4Mn226 (CorsFe2s)11.1Mn22.3 (CorsFers)11.4Mn226 (CorsFers)n.1Mn223 (CorsFers)n.4Mnze (CorsFe2s)rsMm22 (CorsFe2s)18Mn22 (ConsFees)nsMn22 (CorsFezs)18Mn22 Composition 5 Composition 4 FerraPto2Mnzz Fen.1PtosMnz FengPt2Mn22 $Fe_{18}Mn_{22}$ Composition 3 Fen.1PtosMn22 FernsPto2Mn22 FenePtaMn22 Fe₁₈Mn₂₂ (NisoFezo)18Mn22 (NisoFezo)18Mnzz (NieoFezo)18Mnzz Composition 2 (NisoFezo)18Mnz2 (NisoFeza)18Mnzz (NisoFezo)7sMnzz (NisoFeau)18Mn22 (NisoFezo)78Mnzz Composition 1 21.413.2 10.6 21.6 21.6 14.6 **B B** 10.2 21.4 21.9 21.7 10.4 10.5 12.5 10.4 21.1 Heat treatment temperature (°C) 260 300 400 Sample Element No. type િ ગ ા ા 129 130 132 131

TABLE 8a)-1

(ConsFees)16 4Mn23 6 (ConsFees)149Mn25 1 (CorsFezs)16.4Mnzs6 (CorsFezs)149Mnzs1 (CorsFezs)164Mn236 (CorsFezs)149Mn23.1 (CorsFezs) 16.4Mn23.6 (CorsFezs) 14.9Mn25.1 (CorsFezs)rsMnzz (CorsFe2s)raMn22 (CorsFe2s)18Mn22 (CorsFe2s)rsMn22 Composition 6 (CorsFers)11.1Mnr23 (CorsFers)11.4Mnr28 (CorsFers)11.1Mnr23 (CorsFers)11.4Mn226 (CorsFess)11.1Mn223 (CorsFess)11.4Mn226 (ConsFers)m1Mn223 (ConsFers)m4Mn226 (CorsFe2s)reMn22 (CorsFezs)18Mn22 (ConsFers) 18Min 22 (CorsFe2s)18Mn22 Composition 5 Composition 4 FeasPtoMnz FeeePt10Mn22 Fe41Pt31Mn22 Fen.PtnMn22 Composition 3 FeesPt10Mn22 Fe41Pt31Mn22 FessPt40Mnz2 FenPtrMnz (NisoFezo)7slMnzz (NixoFe2o)nsMn22 (NisoFezo)nsMnzz (NisoFezo)78Mnzz Composition 2 (NisoFezo)nsMnzz (NisoFezo)18Mnzz (NisoFezo)isMnzz (NisoFezo)18Mnzz Composition 1 16.9 22.3 19.9 14.6 18.1 22.1 12.8 18.2 9.5 17.6 13.4 10.4 16.2 ₹3 9.6 10.7 8.1 Heat treatment temperature (°C) 400 350 de 1.t. 40 350 SG rt Element type ા ા ા ં Sample ż 133 13 135 136

TABLE 8a)-2

(Co15Fe25)99.8Rho.2 (Co15Fe25)99.1Rho.3 Composition 3 (CorsFers)91Rh3 ConsFers Composition 2 CosoPtso CosoPtso CosoPtso CosoPtso Composition 1 CosoPtsu CosoPtso CosoPtso CosoPtso 18.8 35.6 36.6 15.4 10.5 18.5 35.9 36.6 26.5 25.9 18.1 36.2 36.4 35.6 30.1 36.5 37.1 15.1 9.9 MR (%) Heat treatment temperature (°C) 7. r.t. 300 350 400 Element type Ŧ ਚ ਚ ਚ TABLE 8b)-1 Sample No. 140 137 138 139

Composition 9 CosoPtso CosoPtso CosoPtso CosoPtsoComposition 8 CosoPtso CosoPtso CosoPtso CosoPtso(Co15Fe25)99.8Rho.2 (Co15Fe25)99.1Rho.3 Composition 7 (CorsFe2s)97Rh3 CorsFe2s (Co15Fe25)99.8Rho.2 (Co15Fe25)99.1Rho.3 Composition 6 (CoreFers)91Rh3 Co₇₅Fe₂₅ Composition 5 NisoFe20 NisoFezo NisoFe20 Ni80Fe20 (Co15Fe25)99.8Rho.2 (Co15Fe25)99.1Rho.3 (CoreFere)91Rh3 Composition 4 Co15Fe25 35.6 36.6 36.6 18.9 36.5 15.1 18.8 10.5 18.5 35.9 26.5 25.9 18.1 36.4 35.6 37.1 15.4 6.6 8 8 8 30.1 Heat treatment temperature (°C) 260 300 350 400 300 350 400 r.t. 260 300 350 400 r.t. 360 360 400 260 r. r. r.t. Sample Element No. type ਚ . ∂ 3 ᡇ 137 138 139 140

TABLE 8b)-2

TABLE 8b)-3

Composition 3				(Co15Fe25)11Rh29					(Co15Fe25)41Rh59		-	(Co15Fe2s)38Rhs2							
Composition 2				CosoPtso					CosoPtso			CosoPtso							
Composition 1	-			CosoPtso					CosoPtso			CosoPtso							
MR (%)	16.5	16.1	30.1	32.4	34.5	34.3	15.2	25.7	26.6	30.3	29.8	10.3	22.1	23.5	16.1	11.2			
Heat treatment temperature (°C)	rt.	rt. 260 300 350 400					rt. 260 300 350 400				r.t.	260	300	350	400				
Sample Element No. type		 I	(P							ᡇ		L	Ŧ						
Sample No.		141				142			143						144				

Composition 9 CosoPtso CosoPtso. CosoPtso CosoPtso Composition 8 CosoPtso CosoPtso CosoPtsoCosoPtso (CorsFe25)85Rh15 (Co15Fe25)71Rh29 (CorsFezs)41Rhs9 (CorsFers)38Rhe2 Composition 7 (Co15Fe25)85Rh15 (CorsFers)71,Rh29 Composition 6 (Co15Fe25)41Rh59 (Co15Fe25)38Rhe2 Composition 5 NisoFe20 NisoFe20. NisoFezo NisoFezo (Co15Fe25)85Rh15 Composition 4 (Co15Fe25)11Rh29 (Co15Fe25)41Rh59 (Co16Fe25)38Rhe2 16.5 26.6 30.3 33.2 34.2 36.6 34.5 34.3 16.1 30.1 32.4 15.2 25.7 29.8 10.3 22.1 23.5 8 <u>M</u> 8 16.1 Heat treatment temperature (°C) r.t. 260 300 350 400 rt. 300 350 400 300 350 400 7.t. 260 300 350 400 r.t. Element type € ਚ ਚ ਚ Sample No. 141 142 143 144

TABLE 8 b)-4

(CosoFe10)99.1Pto.15Mno.15 (CosoFe10)99.55Pto.3Mno.15 (Co30Fe10)99.8Pto.1Mno.1 (Co30Fe10)99.7Pto.2Mno.1 (C090Fe10)99.85Mno.15 (CosoFe10)ssPt1Mn1 (CosoFe10)s1Pt2Mn1 (CosoFeso)99.9Pto.1 . Composition 3 (CosoFe10)99Mn1 CosoFe 10 (CosoFeso)99.8Pto.2 (CosoFeso)99.7Pto.3 Composition 2 (CosoFeso)91Pt3 CosoFeso (CosoFeso)99.8Pto.2 (CosoFeso)89.7Pto.3 Composition 1 (CosoFeso)97Pts CosoFeso 34.3 9.5 15.5 35.2 28.4 36.7 32.8 29.9 32.1 34.1 8.5 15.3 32.4 11.1 24.6 16.3 35.2 33.1 Heat treatment temperature (°C) 260 300 350 400 400 400 400 7.t. 350 350 350 350 350 400 400 400 Element type ਚ ਰ ਚੇ ਚ Sample No. 145 146 147 148

TABLE 8c)-1

(CosoFeso)99.8Pto.2 | (CosoFeso)99.8Pto.2 (CosoFeso)99.1Pto.3 | (CosoFeso)99.1Pto.3 Composition 9 (CosoFeso)97Pt3 CosoFeso Composition 8 (CosoFeso)91Pts CosoFeso (CosoFe10)99.7Pto.15Mn0.15 (CosoFe10)99.55Pto.3Mn0.15 (CosoFe10)99.8Pto.1Mno.1 (CosoFe10)99.1Pto.2Mno.1 (C090Fe10)99.85Mno.15 (CosoFe10)ssPt1Mn1 (CosoFe10)97Pt2Mn1 (CosoFe10)39.8Mno.1 (CosoFe10)99Mn1 Composition 7 CosoFe10 (Fe51Ni43)99.81ro.2 (Fe54Ni46)99.81ro.2 (Fess.8Ni46.2)97.3 [r2.7 (Fe51Ni4s)99.81ro.2 (Fe54Ni48)99.81ro.2 (Fese.9Ni43.1)97.1 Ir2.9 (Fe60Ni40)99.1 Iro.3 (Fe60Ni40)99.8 Iro.2 Composition 6 (Fe60Ni40)971r3 Fe54N146 Fe60Ni40 Fest Nias Composition 5 Ni78.9Fe21.1 Ni71.8Fe22.2 Ni78.9Fe21.1 Ni77.8Fe22.2 Ni78.9Fe21.1 Ni77.8F 822.2 Ni78.9Fe21.1 Ni71.8Fe22.2 NisoFe20 NisoFezo NisoFe20 NisoFezo (Fess.9Ni43:1)97.1Ir2.9 (FestNi43)99.81ro.2 (FestNi46)99.81ro.2 (Fess. 8 Ni 46. 2) 97. 3 Irz. 7 (Fe60Ni40)99.8Iro.2 (Fe60Ni40)99.1 Iro.3 (Fe54Ni48)99.1 Iro.3 (Fe57Ni43)99.7 Iro.3 Composition 4 (Fe60Ni40)97 Ir3 Feer Ni43 FesaNias Fee0Ni40 32.8 29.9 32.4 35.2 15.3 33.1 24.6 15.1 34.3 15.5 28.4 % MR 32.1 34.1 10.1 8.5 11.1 9.5 35.2 16.3 36.7 treatment temperature (°C) Heat 260 300 400 280 300 tr ند 300 300 350 260 260 400 350 400 Element type Ŧ ਚ ਚ ÷ TABLE 8c)-2 Sample No. 145 146 147 148

(CosoFe10)61Pt19.6Mn19.5 (CosoFe10)41.5Pt39Mn19.5 (CosoFe10)81Pts.sMns.s (CosoFe10)11.sPt19Mns.s (CosoFe10)ssPt21Mn21 (CosoFe10)31Pt42Mn21 (CosoFe10)soPtsMns (CosoFe10)ssPt10Mns (CosoFe10)s0.5Mn9.5 (C090Fe10)80.5Mn19.5 (CosoFe10)ssMns (C090Fe10)78Mn21 Composition 3 (CosoFeso)85Pt15 (Co50Fe50)38Pt62 Composition 2 (CosoFeso)11Pt29 (Co50Fe50)41Pt59 (CosoFeso)38Pte2 (CosoFeso)85Pt15 (CosoFeso)41Pts9 Composition 1 (CosoFeso)11Pt29-17.5 39.2 13.2 25.9 26.3 14.2 12.5 42.4 42.6 38.1 16.9 37.8 38.2 38.1 15.2 34.3 34.5 33.6 33.1 Heat treatment temperature (°C) 350 400 r.t. 260 300 400 260 300 300 400 400 400 Element type æ ਚ ਚ ᡇ. TABLE 8c)-3 Sample No. 149 150 151 152

(CosoFeso)8sPt1s Composition 9 (CosoFess)711Pt29 (CosoFeso)41Pts9 (CosoFeso)38Pte2 (CosoFeso)85Pt15 (CosoFeso)41 Pts9 Composition 8 (CosoFeso)11Pt29 (CosoFeso)38Pts2 (CosoFe10)81Pt9.5Mn9.5 (CosoFe10)11.5Pt18Mn9.5 (CosoFe10)41.5Pt39Mn19.5 (C090Fe10)61Pt19.5Mn19.5 (CosoFe10)85Pt10Mns (CosoFe10)58Pt21Mn21 (CosoFe10)80.5Mn19.5 (CosoFe10)31Pt42Mn21 CosoFe10)30Pt1Mn5 (CosoFe10) so.s Mn9.s (CosoFe 10)85Mns (CosoFe10)19Mn21 Composition 7 (Fess 9 Ni42.1) 72.4 Lr27.8 (Fest 9 Ni48.1) 73.9 Lr28.1 (Fess 2Ni46.8) 43.9 lrse.1 (Fe47.2 Ni51.8) 46.9 lrss.1 (Fese.sNi43.s)85.1Ir14.3 (Fe51.8Ni48.2)36.3Ir63.7 (Fess. 1 Ni46.9)86.5 Ir. 13.5 (Fe44.9Ni55.1)39.7 Ireo.3 (Fe60Ni40)41Ir59 Composition 6 (FeeoNi40)851r15 (Fe60Ni40)71 Ir29 (Fe60Ni40)41 Ir59 Composition 5 Ni_{78.9}Fe_{21.1} Nin.8F 622.2 Ni78.9Fe21.1 Ni71.8Fe22.2 Ni78.9Fe21.1 Ni77.8Fe22.2 Ni78.9Fe21.1 NisoFezo Ni77.8Fe22.2 NisoFezo NisoFezo NisoFe20 (Fe56.5Ni43.5)85.7Ir14.3 (F947.2 Nis. 8) 48.9 Irss. 1 (Fee1.8Ni48.2)36.31r63.7 (Fess.1 Ni46.9)86.51r13.5 (Fe51.9Ni48.1)13.9Ir26.1 (Fe53.2Ni46.8)43.9Ir56.1 (Fe44.9Ni55.1)39.7Ir60.3 (Fe55.9 Ni44.1) 72.4 Ir 27.6 Composition 4 (Fe60Ni40)11Ir29 (FegoNi40)851r15 (Fe60Ni40)41 Ir59 (Fe60Ni40)33Ir61 37.8 34.3 17.5 39.2 42.6 37.9 33.6 16.9 38.2 38.1 34.5 14.2 42.4 38.1 15.2 33.1 25.9 13.2 26.3 12.5 % % temperature (°C) treatment Heat 7.t. 300 350 260 300 400 400 260 300 350 r.t. 8 rt. 260 350 r.t. Element type ਚ ð Ŧ ਚ Sample No. 149 150 151 152

TABLE 8c)-4

(NisoFeso)99.8Pto.2 (NisoFeso)99.1Pto.3 Composition 3 (NisoFeso)91Pt3 NisoFeso Composition 2 NisoFeso NisoFeso NisoFeso NisoFeso Composition 1 CosoFeso CosoFeso CosoFeso CosoFeso 31.3 16.7 12.2 17.3 30.6 31.1 16.5 13.1 17.5 31.2 32.4 27.6 25.8 18.2 32.9 33.4 31.3 Heat treatment temperature (°C) 260 300 350 400 400 400 400 r.t. 300 350 400 7.t. 260 300 350 400 Element type ા િ ા ા Sample No. 153 154 155 156

TABLE 8d)-1

Composition 9 CosoPdso CosoPdso CosoPdso CosoPdso Composition 8 CorsFe2s CorsFe2s CorsFers Co25Fe25 (Co15Fe25)99.8Pto.14Mno.03Cro.03 (Co15Fe25)99.1Pto.2Mno.05Cr0.05 (Co15Fe25)97Pt2Mn0.5Cr0.5 Composition 7 CorsPt2s Composition 6 CorsFe25 CorsFe25 ConsFe25 CorsFe25 Composition 5 NisoFezo Ni80Fe20 $Ni_{80}Fe_{20}$ NisoFe20 Composition 4 NisoFeso NisoFeso NisoFeso NisoFeso 31.2 25.8 33.4 30.4 16.7 12.2 17.3 30.6 31.1 16.5 13.1 32.4 18.2 32.9 **8 8** Heat treatment temperature (°C) 260 300 400 Element type ુ • ි . ા ા TABLE 8d)-2 Sample No. 153 154 155 156

(NisoFeso)85Pt15 Composition 3 (NisoFeso)11 Pt29 (NisoFeso)41Pts9 (NisoFeso)38Pt62 Composition 2 NisoFeso NisoFeso NisoFeso NisoFeso Composition 1 CosoFeso CosoFeso CosoFeso СозоГезо 31.1 32.2 32.7 17.5 29.3 29.7 31.3 15.6 25.4 26 27.9 % M % 31.5 20.4 21.7 26.1 12.1 260 300 350 400 1.t. r.t. 260 350 400 Element type ા િ ં ં TABLE 8d)-3 Sample No. 157 158 159 160

Composition 9 CosoPdso CosoPdso CosoPdso CosoPdso Composition 8 Co₇₅Fe₂₅ CorsFe2s ConsFe2s Co₇₅Fe₂₅ (Co15Fe25)38Pt41Mn10.5Cr10.5 (Co15Fe25)85Pt10Mn2.5Cr2.5 (CorsFe2s)41Pt39Mn10Cr10 (CorsFe2s)71Pt19MnsCrs Composition 7 Composition 6 CorsFe25 CorsFe2s CorsFe2s CorsFe25 Composition 5 NisoFezo NisoFe20 NisoFezo NisoFezo Composition 4 NisoFeso NisoFeso NisoFeso NisoFeso 30.5 32.2 32.7 15.6 17.5 29.3 29.7 31.3 25.4 26 27.9 20.4 21.7 17.2 13.5 MR % 26.1 12.1 Heat treatment temperature (°C) 260 300 400 260 300 400 400 400 400 400 7.t. 300 350 400 Element type ા ા ા ા Sample No. 157 159 160 158

TABLE 8d)-4

In the samples shown in Table 5a), Re is added to the vicinity of each of the interfaces of the non-magnetic layer. According to Table 5a), it is preferable that Re has a concentration of 3 to 30 at%. However, the Mn diffusion is not suppressed here. One of the reasons for this is that Re is not added to the vicinity of the interface with the antiferromagnetic layer. The same tendency can be obtained by replacing Re with Ru, Os, Rh, Ir, Pd, Pt, Cu, Au or the like. Moreover, the same tendency can be obtained by modifying the ferromagnetic layers to the above compositions.

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In the samples shown in Table 5b), another element is added to both sides of the non-magnetic layer. This can provide the same effect as well. Moreover, the same effect can be obtained by replacing Ru in Table 5b) with Tc, Re, Rh, Ir, Pd, Pt, Ag or Au and replacing Os with Tc, Re, Rh, Ir, Pd, Pt, Cu or Au. The modification of the ferromagnetic layers to the above compositions also can provide the same tendency.

In the samples shown in Table 5c), Pt and Cu are added only to one of the interfaces of the non-magnetic layer. This can provide the same tendency as well. Moreover, the same tendency can be obtained by replacing (Pt, Cu) in Table 5c) with Tc, Re, Rh, Ir, Pd, Pt, Ag, Au, (Ru, Ir), (Pt, Pd), (Pt, Au), (Ir, Rh), (Ru, Pd), (Tc, Re, Ag), (Ru, Os, Ir), (Rh, Ir, Pt), (Pd, Pt, Cu), (Cu, Ag, Au), (Re, Ru, Os), (Ru, Rh, Pd), (Ir, Pt, Cu) or (Re, Ir, Ag). The modification of the ferromagnetic layers to the above compositions also can provide the same tendency.

Tables 5d) to 8a) show the results obtained when Mn and Pt are added. Table 5d) corresponds to the addition of Mn in an amount of zero at%. Tables 6a) to 8a) show the results of a change in amount of Pt according to the addition of Mn in an amount of 0.2, 0.5, 1, 2, 5, 8, 12, 19 or 22 at%.

There is a little Mn, which is diffused from the antiferromagnetic layer, at the interface in a region containing a small amount of Pt. However, the diffusion can be suppressed by adding Pt.

Tables 8b) to 8d) show the measurements on elements, each having a plurality of non-magnetic layers. Even if a plurality of barriers are present due to the non-magnetic layers, the MR characteristics after heat treatment can be improved by controlling the composition in the vicinity of either of the interfaces of at least one of the non-magnetic layers.

Table 9a) shows the ratios of MR ratios of each sample including Mn and Pt after heat treatment at 350°C and 400°C to MR ratios of a sample to

which neither Mn nor Pt is added (i.e., the sample 57).

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In Table 9a), the amounts of Pt and (Pt + Mn) correspond to the amount of each element in the composition 4 of a sample before heat treatment.

Table 9b) shows the ratios of MR ratios of each sample to MR ratios of a sample in which the amount of Pt is zero for each addition of Mn.

Favorable characteristics were obtained when the amount of addition of Pt was 0.3 to 60 at% and that of Mn was not more than 20 at%, particularly in the range of Mn < Pt. It was confirmed that the characteristics might be more improved by simultaneously adding Mn and Pt than by adding Pt alone in a region where Mn was 8 to 5 at% or less and Mn < Pt. The same tendency was obtained by an element to which Cr or (Mn, Cr) was added with a ratio from 1:0.01 to 1:100 instead of Mn. Moreover, the same tendency was obtained by adding the elements used in Tables 4a) to 5c) instead of Pt. Further, the same tendency was obtained by using the ferromagnetic layers in Table 4.

Some elements (not shown in Tables 4a) to 9b)), each having a composition between the samples shown in Tables, were produced. These elements also had the same tendency.

Tables 4a) to 9b) show the results of heat treatment up to 400°C. However, some samples were heat-treated at 400°C to 540°C in increments of 10°C, thus measuring the MR characteristics. Consequently, the magnetoresistive element that included the additional element M¹ such as Pt in an amount of 0.3 to 60 at% had excellent MR characteristics after heat treatment up to 450°C as compared with the element that did not include the element M¹. In particular, when the amount of addition was 3 to 30 at%, excellent MR characteristics were obtained after heat treatment up to 500°C as compared with the element that did not include the element M¹.

The same measurement was performed on the element to which Mn and Cr (the additional element M^2) were added simultaneously with M^1 . Consequently, the magnetoresistive element that included 0.3 to 60 at% of M^1 and achieved $M^2 < M^1$ had relatively excellent MR characteristics after heat treatment up to 450°C. Moreover, the element that included 3 to 30 at% of M^1 and less than 8 at% of M^2 and achieved $M^2 < M^1$ had relatively excellent MR characteristics after heat treatment up to 500°C as compared with the element that included neither M^1 and M^2 .

The above description shows the results obtained when a AlOx film formed with natural oxidation is used as the non-magnetic layer. However, the same tendency can be obtained by using the following films as the non-magnetic layer: AlO with plasma oxidation; AlO with ion radical oxidation; AlO with reactive evaporation; AlN with natural nitridation; AlN with plasma nitridation; AlN with reactive evaporation; BN with plasma nitridation or reactive evaporation; TaO with thermal oxidation, plasma oxidation, or ion radical oxidation; AlSiO with thermal oxidation, natural oxidation, or plasma oxidation; and AlON with natural oxynitridation, plasma oxynitridation, or reactive sputtering.

The same tendency can be obtained by using FeMn, NiMn, IrMn, PtMn, RhMn, CrMnPt, CrAl, CrRu, CrRh, CrOs, CrIr, CrPt, or TbCo as the antiferromagnetic layer instead of PdPtMn.

The same tendency can be obtained by using Rh (thickness: 0.4 to 1.9 nm), Ir (0.3 to 1.4 nm), or Cr (0.9 to 1.4 nm) as the non-magnetic metal instead of Ru (0.7 to 0.9 nm).

Basically the same tendency can be obtained from each of the elements having the configurations shown in the drawings.

20 Example 3

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In this example, magnetoresistive elements were produced by the same methods of film forming and processing as those in Examples 1 and 2. The composition was measured in the same manner as that in Example 2.

A AlON film (thickness: 1.0 to 2 nm) was used as the non-magnetic layer. The AlON film was produced by oxynitriding an Al film in a chamber filled with a mixed gas of pure oxygen and high purity nitrogen with a radio of 1:1. Rh (1.4 to 1.9 nm) was used as the non-magnetic metal film, and PtMn (20 to 30 nm) was used as the antiferromagnetic layer.

The element configuration and the ferromagnetic layers were the same as those of the samples shown in Tables 5d) to 8a). In this example, the effect of adding Ta and N was measured in addition to Pt and Mn.

Like Example 2, the characteristics after heat treatment up to 540°C were examined. Here, the measurements at 350°C and 400°C, both indicating distinctive features, were described. In this example, a coercive force of the free layer was measured as the magnetic characteristics. Tables 10 to 22 plot the coercive force against the composition of elements added to each of the interfaces.

The magnetic characteristics of the samples whose coercive forces are not shown in Tables cannot be measured. The addition of Ta and N improves the soft magnetic characteristics. However, when the amount of non-magnetic additives is not less than about 70 at%, it is impossible to measure the magnetic characteristics.

The MR characteristics of the samples in Tables 10, 11, 12, 15, 16, 19 and 20 are within \pm 10% after heat treatment, compared with the element that does not include Ta and N. The MR characteristics of the samples in Tables 13, 17 and 21 are degraded by about 10 to 20%, and those of the samples in Tables 14, 18 and 22 are degraded by about 50 to 60%.

The same tendency can be obtained by replacing Ta with Ti, Zr, Hf, V, Nb, Mo, W, Al, Si, Ga, Ge, In or Sn. Moreover, the same tendency can be obtained by replacing N with B, C or O.

15 Example 4

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In this example, magnetoresistive elements were produced by the same method of film forming and processing as those in Examples 1 and 2. The composition was measured in the same manner as that in Example 2.

A AlOx film (thickness: 1.0 to 2 nm) was used as the non-magnetic layer. The AlOx film was produced by oxidizing an Al film with an ion radical source of O. Ir (1.2 to 1.4 nm) was used as the non-magnetic metal layer, and NiMn (30 to 40 nm) was used as the antiferromagnetic layer.

The element configuration and the ferromagnetic layers were the same as those of the samples shown in Tables 4 to 8. In this example, Pt, Pr and Au were added to examine the MR characteristics after each of the heat treatments and the stability of solid solution.

The solid solution was evaluated in the following manner. First, the elements were heat-treated at different temperatures of 350°C, 400°C, 450°C and 500°C. Then, the composition at the interfaces of the non-magnetic layer of each of the elements was determined, e.g., by XPS analysis after AES depth profile, SIMS, and milling. Next, alloy samples having the composition thus determined was produced separately, which then were heat-treated in the atmosphere of a reduced pressure (10.5 Pa) at 350°C, 400°C, 450°C and 500°C for 24 hours. The surfaces of the alloy samples were etched chemically and observed with a metallurgical microscope. After etching, ion milling was performed in the atmosphere of a reduced pressure, followed by structural observation with a scanning

electron microscope (SEM) and in-plane composition analysis with EDX. Finally, the alloy samples were evaluated whether they had a single phase based on the measurements.

When composition distribution and a plurality of phases were observed in the alloy sample, whose heat treatment temperature and composition corresponded to those of the magnetoresistive element, the MR characteristics of this element were improved by about 30 to 100%, compared with the element that did not include M¹ or the like. When the alloy sample showed a single phase, the MR characteristics of the corresponding element were improved by about 80 to 200%, compared with the element that included no additional element. The element that corresponded to the alloy sample having a stable single phase provided even more favorable MR characteristics after heat treatment.

Example 5

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Using the samples in Tables 4d), 5a), 5c), and 5d) of Example 2, the diffusion effect of Mn observed after heat treatment was controlled by appropriately changing the distance between the interface of antiferromagnetic layer/ferromagnetic layer and the interface of ferromagnetic layer/non-magnetic layer and heat treatment temperatures. Here, the heat treatment temperature was 300°C or more. This control was performed so that Mn at the interfaces of the non-magnetic layer was 20 to 0.5 at% after heat treatment. When the distance was less than 3 nm, the content of the magnetic elements (Fe, Co, Ni) was reduced to 40 at% or less after heat treatment even with the addition of Pt or the like, resulting in a significant degradation of the MR characteristics. When the distance was more than 50 nm, heat treatment at 400°C or more was required only for increasing the content of Mn at the interfaces by 0.5 at%. Since the distance was too long, a sufficient effect of fixing the magnetization directions of the ferromagnetic layers was not obtained from the antiferromagnetic layer, resulting in a significant degradation of the MR characteristics after heat treatment.

TABLE 9a)

1	Amou	int of Mn	1	2	3	4	5	6	7	8
		Amount of Pt	0	0.2	0.3	3	15	29	59	62
TABLE	0	Amount of Pt+Mn	0	0.2	0.3	3	15	29	59	62
5d)		350°C	1	1.02	1.44	1.52	1.61	1.54	1.46	0.98
	*.	· 400°C	· 1	1:02	1.92	1.99	2.45	2.21	1.95	1.05
		Amount of Pt	0	0.2	0.3	2.8	14.8	28.8	58.8	61.8
TABLE	0.2	Amount of Pt+Mn	0.2	0.4	0.5	3	. 15	29	59	62
6a)		350°C	1	1.03	1.56	1.78	1.81	1.68	1.51	0.99
		400°C	1	1.03	2.21	2.43	2.62	2.51	2.27	1.06
		Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58:5	61.5
TABLE	0.5	Amount of Pt+Mn	0.5	0.7	0.8	3	15	29	59	62
6b)		350°C	1	1.01	1.46	1.77	1.97	1.9	1.74	1
		400°C	1	1.01	1.98	2.42	2.73	2.71	2.5	1.06
		Amount of Pt	0	0.2	0.3	2	14	28	58	61
TABLE	1	Amount of Pt+Mn	1	1.2	1.3	3	15	. 29	59	62
6c)		350°C	1	1.01	1.45	1.76	2.07	1.96	1.84	1.04
		400°C	1	1.01	1.91	2.4	2.9	2.81	2.61	1.1
•		Amount of Pt	0	0.2	0.3	2	13	27	57	60
TABLE	2	Amount of Pt+Mn	2	2.2	2.3	4	15	29	59	62
6d)		350°C	1	1.01	1.44	1.76	2.17	2.06	1.98	1.06
		400°C	1	1.01	1.9	2.39	3.13	2.98	2.81	1.12
		Amount of Pt	0	0.2	0.3	. 2	10	24	54	57
TABLE	5	Amount of Pt+Mn	5	5.2	5.3	7	15	29	59 ·	62
7a)		350°C	1	1.01	1.43	1.7	2.16	1.98	1.86	1.05
		400°C	1	1.01	1.89	2.21	3.04	2.92	2.73	1.11
TABLE	,	Amount of Pt	0	0.2	0.3	2	7	21	51	54
7b)	8	Amount of Pt+Mn	8	8.2	8.3	10	15	29	59	62
		350°C	1	1.01	1.39	1.6	1.8	1.69	1.59	1.02
		400°C	1	1.01	1.8	2.09	2.6	2.38	2.27	1.07
		Amount of Pt	0	0.2	0.3	2	7	17	47	50
TABLE	12	Amount of Pt+Mn	12	12.2	12.3	14	19	29	59	62
7c)		350°C	1	1.01	1.38	1.51	1.6	1.58	1.47	1
		400°C	1	1.01	1.77	2	2.2	2.17	2	1.02
		Amount of Pt	0	0.2	0.3	2	7	10	40	43
TABLE	19	Amount of Pt+Mn	19	19.2	19.3	21	26	29	59	62
7d)		350°C	1	1	1.36	1.41	1.52	1.44	1.33	0.94
		400°C	1	1	1.71	1.8	1.95	1.87	1.71	0.99
		Amount of Pt	0	0.2	0.3	2	7	10	37	40
TABLE	22	Amount of Pt+Mn	22	22.2	22.3	24	29	32	59	62
8a)		350°C	1	0.99	1.1	1.11	1.13	1.1	1.01	0.86
	,	400°C	1	0.99	1.16	1.19	1.21	1.2	0.99	1.01

TABLE 9b)

!	Amou	ınt of Mn	1	2	3	4	5	6	7	8
		Amount of Pt	0	0.2	0.3	3	15	29	59	62
TABLE	0	Amount of Pt+Mn	0	0.2	0.3	3	15	29	59	62
5d)		350°C	1	1.02	1.44	1.52	1.61	1.54	1.46	0.98
		400°C	1	1.02	1.92	1.99	2.45	2.21	1.95	1.05
		Amount of Pt	0	0.2	0.3	2.8	14.8	28.8	58.8	61.8
TABLE	0.2	Amount of Pt+Mn	0.2	0.4	0.5	3	15	29	59	62
6a)		350°C	1	1.03	1.56	1.78	1.81	1.68	1.51	0.99
		400°C	1	1.03	2.21	2.43	2.62	2.51	2.27	1.06
		Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
TABLE	0.5	Amount of Pt+Mn	0.5	0.7	0.8	3	15	29	59	62
6b)		350°C	1	1.01	1.46	1.77	1.97	1.9	1.74	1
		400°C	1	1.01	1.98	2.42	2.73	2.71	2.5	1.06
		Amount of Pt	0	0.2	0.3	2	14	28	58	61
TABLE	1	Amount of Pt+Mn	1	1.2	1.3	3	15	29	59	62
6c)		350°C	1	1.01	1.45	1.76	2.07	1.96	1.84	1.04
		400°C	1	1.01	1.91	2.4	2.9	2.81	2.61	1.1
		Amount of Pt	0	0.2	0.3	2	13	27	57	60
TABLE	2	Amount of Pt+Mn	2	2.2	2.3	4	15	29	. 59	62
6d)		350°C	1	1.01	1.44	1.76	2.17	2.06	1.98	1.06
		400°C	1	1.01	1.9	2.39	3.13	2.98	2.81	1.12
		Amount of Pt	0	0.2	0.3	2	10	24	54	57
TABLE	5	Amount of Pt+Mn	5	5.2	5.3	7	15	29	59	62
7a)		350°C	1	1.01	1.43	1.7	2.16	1.98	1.86	1.05
		400°C	1	1.01	1.89	2.21	3.04	2.92	2.73	1.11
TABLE		Amount of Pt	0	0.2	0.3	2	7	21	51	54
7b)	8	Amount of Pt+Mn	8	8.2	8.3	10	15	29	- 59	62
		350°C	1	1.01	1.39	1.6	1.8	1.69	1.59	1.02
		400°C	1	1.01	1.8	2.09	2.6	2.38	2.27	1.07
		Amount of Pt	0	0.2	0.3	2	7	17	47	50
TABLE	12	Amount of Pt+Mn	12	12.2	12.3	14	19	29	59	62
7c)		350°C	1	1.01	1.38	1.51	1.6	1.58	1.47	1
		400°C	1	1.01	1.77	2	2.2	2.17	2	1.02
		Amount of Pt	0	0.2	0.3	2	7	10	40	43
TABLE	19	Amount of Pt+Mn	19	19.2	19.3	21	26	29	59	62
7d)		350°C	1	1	1.36	1.41	1.52	1.44	1.33	0.94
,		400°C	1	1	1.71	1.8	1.95	1.87	1.71	0.99
		Amount of Pt	0	0.2	0.3	2	7	10	37	40
TABLE	22	Amount of Pt+Mn	22	22.2	22.3	24	29	32	59	62
· 8a)		350°C	1	0.99	1.1	1.11	1.13	1.1	1.01	0.86
	L	400°C	1	0.99	1.16	1.19	1.21	1.2	0.99	1.01

TABLE 10 (Ta = 0, N = 0)

					-				
Amo	unt of Mn								
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	0	0.2	0.3	3	15	29	59	62
0	350°C	98	98	99	113	127 .	147	196	196
	400°C	88	88	89	101	115	132	176	176
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	0.5	0.7	0.8	3	15	29	59	62
0.5	350°C	97	97	98	112	126	146	194	194
	400°C	87	87	88	100	114	131	175	175
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	1	1.2	1.3	3	15	29	59	62
1	350°C	93	93	94	107	121	140	186	186
	400°C	84	84	85	96	109	126	168	168
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	5	5.2	5.3	7	15	- 29	59	62
5	350°C	· 88	88	89	101	115	132	176	176
	400°C	79	79	80	91	103	119	159	159
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	8	8.2	8.3	10	15	29	59	62
8	350°C	93	93	94	107	121_	140	186	186
	400°C	84	84	85	96	109_	126	168	168
	Amount of Pt	0	0.2	0.3	2	7	10	40	43
	Total amount of additional elements	19	19.2	19.3	21	26	29	59	62
19	350°C	96	96	97	110	125	144	192	192
	400°C	86	86	87	99	112	130	173	173
	Amount of Pt	0	0.2	0.3	2	7	10	37	40
	Total amount of additional elements	22	22.2	22.3	24	29	32	59	62
22	350°C	100	100	101	115	130	150	200_	200_
	400°C	90	90	91	103	117	135	180_	180

TABLE 11(Ta = 1, N = 0)

Am	ount of Mn			· .					
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	1	1.2	1.3	4	16	30	60	63
0	350°C	99 _	. 99	100	.114	129	149.	198	198
	400°C	89	89	90	102	116	134	178	178
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	1.5	1.7	1.8	4	16	30	60	63
0. 5	350°C	98	98	99	113	127	147	196	196
	400°C	88	88	89	101	115	132	176	176
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	2	2.2	2.3	4	16	30	60	63
1	$350^{\circ}\mathrm{C}$	94	94	95	108	122	141	188	188
	400°C	85	85	85	97	110	127	169	169
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	6	6.2	6.3	8	16	30	60	63
5	350°C	89	89	90	102	116	134	178	178
	400°C	80	80	81	92	104	120	160	160
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	9	9.2	9.3	11	16	30	60	63
8	350°C	94	94	95	108	122	141	188	188
	400°C	85	85	85	97	110	127	169	169
	Amount of Pt	. 0	0.2	0.3	2	7	10	40	43
	Total amount of additional elements	20	20.2	20.3	22	27	30	60	63
19	350°C	97	97	98	112	.126	146	194	194
	400°C	87	87	88	100	114	131	175	175
	Amount of Pt	0	0.2	0.3	2	7	10	37	40
	Total amount of additional elements	23	23.2	23.3	25	30	33	60	63
22	350°C	101	101	102	116	131	151	202	202
	400°C	91	91	92	105	118_	136	182	182

TABLE 12 (Ta = 15, N = 0)

Α.									
Amo	unt of Mn				ı — <u>-</u>				
	Amount of Pt Total amount of	0 15	0.2 15.2	0.3 15.3	3 18	15 30	29 44	59 74	62 77
	additional elements	19	10.2	10.5	10	30	44	74	11
0	350°C	58	58	59	67	75	87	_	
	400°C	52	52	53	60	68	78	_	
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5.	58.5	61.5
	Total amount of additional elements	15.5	15.7	15.8	18	30	44	74	77
0.5	350°C	57	57	58	66	75	86		
	400°C	52	52	52	59	67	78	_	
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	16	16.2	16.3	18	30	44	74	77
1	350°C	55	55	56	63	72	83	_	_
	400°C	50	50	50	57	64	74	<u> </u>	_
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	20	20.2	20.3	22	30	44	74	77
5	350°C	52	52	53	60	68	78	_	_
	400°C	47	47	47	54	61	70	_	_
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	23	23.2	23.3	25	30	44	74	77
8	350°C	55	55	56	63	72	83		
	400°C	50	50	50	57	64	74		
	Amount of Pt	0	0.2	0.3	2	7 .	10	40	43
	Total amount of additional elements	34	34.2	34.3	36	41	44	74	77
19	350°C	57	57	57	65	74	85	_	
	400°C	51	51	52	59	67	77	— .	
	Amount of Pt	0	0.2	0.3	2	7	- 10	37	40
	Total amount of additional elements	37	37.2	37.3	39	44	47	74	77
22	350°C	59	59	60	68	77	89	_	_
	400°C	53	53	54	61	69	80	_	_

TABLE 13 (Ta = 29, N = 0)

				(1a -	20, 11				 -
Amo	unt of Mn				····				
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	29	29.2	29.3	32	44	58	88	91
0	350°C	22	22	22	25	. 29	33 .	. —	
	400°C	20	20	20	23	26	30	_	
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	29.5	29.7	29.8	32	44	58	88	91
0.5	350°C	22	22	22	25	28_	33	_	
	400°C	20	20	20	23	25	29		_
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	30	30.2	30.3	32	44	58	88	91
1	350°C	21	21	21	24	· 27	31		_
	400°C ·	19	19	19	22	24	28		_
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	34	34.2	34.3	36	44	58	88	91
5	350°C	20	20	20	23	26	30		<u> </u>
	400°C	18	18	18	20	23	27		
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	37	37.2	37.3	39	44	58	88	91
8	350°C	21	21	21	24	27	31	_	
	400°C	19	19	19	22	24	28		
	Amount of Pt	0	0.2	0.3	2	7	10	40	43
	Total amount of additional elements	48	48.2	48.3	50	55	58	88	91
19	350°C	22	22	22_	25	28	32		_
	400°C	19	19	20	22	25	29		
	Amount of Pt	0	0.2	0.3	2	7	∙10	37	40
	Total amount of additional elements	51	51.2	51.3	53	58	61	88	91
22	350°C	22	22	23	26	29_	34		
	400°C	20	20	20	23_	26	30	<u> </u>	

TABLE 14 (Ta = 31, N = 0)

Amo	unt of Mn								
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	31	31.2	31.3	34	46	60	90	93
0	350°C	18	18	18	21	23	27	1	_
	400°C	16	16	16	19	21	24	_	_
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	31.5	31.7	31.8	34	46	60	90	93
0.5	350°C	18	18	18	20	23	27	-	
	400°C	16	16	16	18	21	24		– .
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	32	322	32.3	34	46	60	90	93
1	350°C	17	17	17	20	22	26	_	
	400°C	15	15	16	18	20	23	_	
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	36	36.2	36.3	38	46	60	90	93
5	350°C	16	16	16	19	21	24		
	400°C	15	15	15	17	19	22		_
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	39	39.2	39.3	41	46	60	90	93
8	350°C	17	17	17	20	22	. 26	_	_
	400°C	15	15	16	18	20	23		_
	Amount of Pt	0	0.2	0.3	2	7	10	40	43
	Total amount of additional elements	50	50.2	50.3	52	57	60	90	93
19	350°C	18	18	18	20	23	26		_
<u></u>	400°C	16	16	16	18	21	24		
	Amount of Pt	0	0.2	0.3	2	7	10	37	40
	Total amount of additional elements	53	53.2	53.3	55	60	63	90	93
22	350°C	18	18	19	21	24	28	_	
	400°C	17	17	17	19	21	25_	<u> </u>	L

TABLE 15 (Ta = 0, N = 1)

									
Amou	nt of Mn		· · · · · ·						
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of			1.0		10	90	00	CO.
	additional elements	1	1.2	1.3	4	16	30	60	63
0.	350°C	101	101	102	116	131	152	202	202
	400°C	91	91	92	105	118	136	182	182
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of	1.5	1.7	1.8	4	16	30	60	63
0.5	additional elements 350°C		100	101	115	130	150	200	200
0.0	400°C	100 90	90	91	103	117	135	180	180
		0	0.2	$\frac{91}{0.3}$	2	14	28	58	61
	Amount of Pt Total amount of	U	0.2	0.5		14	40	96	OI
	additional elements	2	2.2	2.3	4	16	30	60	63
1	350°C	96	96	97	110	125	144	192	192
	400°C	86	86	. 87	99	112	130	173	173_
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of				,				
	additional elements	6	62	6.3	8 .	16	30	60	63
5	350°C	91	91	92	105	118	136	182	182
	400°C	82	82	83	94	106	123	164	164
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	9	9.2	9.3	11	16	30	60	63
8	350°C	96	96	97	110	125	144	192	192
"	400°C	86	86	87	99	112	130	173	173
	Amount of Pt	0	0.2	0.3	2	7	100	40	43
	Total amount of	U	0.2	0.5		'	10		10.
	additional elements	20	20.2	20.3	22	27	30	60	63
19	350°C	99	99	100	114	129	148	198	198
	400°C	89	89	90	102	116	134	178	178
	Amount of Pt	0	0.2	0.3	2	7	10	37	40
	Total amount of	-							
	additional elements	23	23.2	23.3	25	30	33	60	63
22	350°C	103	103	104	118	134	155	206	206
	400°C	93	93	94	107	121	139	185	185_

TABLE 16 (Ta = 0, N = 10)

Amo	unt of Mn								
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	10	10.2	10.3	13	25	39	69	72
0	350°C	62	62	63	71	81	93	– .	
	400°C	56	56	56	64	73	84		
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of								_
	additional elements	10.5	10.7	10.8	13	25	39	69	72
0.5	350°C	61	61	62	71	80	92		
ļ	400°C	55	.55	56	64	72	83		
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of								
1	additional elements	11	11.2	11.3	13	25	39	69	72
1	350°C	59	59	59	68	77	88		
ļ	400°C	53	53	.54	61	69	80		
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of	1.5	15.0	150	1.7	0.5	90	00	
_	additional elements	15	15.2	15.3	17	25	39	69	72
5	350°C	56	56	56	64	73	84	_	
<u> </u>	400°C	50	50	51.	58	65	75		
	Amount of Pt	. 0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	18	18.2	18.3	20	25	39	69	72
8	350°C	59	59	59	68	77	88	-	-
١٩	400°C	53	53	54	61	69	80	-	
-	Amount of Pt	0	0.2	0.3	2	7	10	40	43
	Total amount of	U .	0.2	0.5	4	'	10	40	45
	additional elements	29	29.2	29.3	31	36	39	69	72
19	350°C	61	61	61	70	79	91	_	_
	400°C	55	55	55	63	71	82	_	_
	Amount of Pt	0	0.2	0.3	2	7	10	37	40
	Total amount of	ŭ	0.=	0.0	_	'	"		•
	additional elements	32	32.2	32.3	34	39	42	69	72
22	350°C	63_	63	64	73	82	95	_	_
	400°C	57	57	57	65	74	85		

TABLE 17 (Ta = 0, N = 19)

Amo	unt of Mn			(1a -		•	- <u></u>		
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	19	19.2	19.3	22	34	48	78	81
0	350°C	25	25	25	29	33	38		
	400°C	23	23	23	26	29	34		
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	19.5	19.7	19.8	22	34	48	78	81
0.5	350°C	25	25	25	28	32	37	_	
	400°C	22	22	22	26	29	33		
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	20	20.2	20.3	22	34	48	78	81
1	350°C	24	24	24	.27	31	36	_	
	400°C	21	21	22	25	28	32	_	_
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
-	Total amount of additional elements	24	24.2	24.3	26	34	48	78	81
5	350°C	23	23	23	26	29	34	_	· -
	. 400°C	20	20	20	23	26	30	_	-
	Amount of Pt	. 0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	27	27.2	27.3	29	34	48	78	81
8	350°C	24	24	24	. 27	31	36		. —
	· 400°C	21	21	22	25	28	32		
	Amount of Pt	0	0.2	0.3	2	7	10	40	43
	Total amount of additional elements	38	38.2	38.3	40	45	48	78	81
19	350°C	25	25	25	28	32	37		
	400°C	22	22	22	25	29	33	_	_
	Amount of Pt	0	0.2	0.3	2	7	10	37	40
	Total amount of additional elements	41	41.2	41.3	43	48	51	78	81
22	350°C	26	26	26	29	33	38	_	_
	400°C	23	23	23	26	30	34	_	_

TABLE 18 (Ta = 0, N = 21)

									
Amo	unt of Mn								
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	21	21.2	21.3	24	36	50	80	83
0	350°C	21	21	21	. 24	27	32		_
	400°C	19	19	19	22	25	28		
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	21.5	21.7	21.8	24	36	50	80	83
0.5	350°C	21	21	21	24	27	31		
	400°C	19	19	19	22	24	28		-
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	22	22.2	22.3	24	36	50	80	83
1	350°C	20	20	20	23	26	30	_	_
	400°C	18	18	18	21	23	27	_	_
	· Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	26	26.2	26.3	28	36	50	80	83
5	350°C	19	19	19	22	25	28	_	
	400°C	17_	17	17	20	22	26	-	_
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	29	29.2	29.3	31	36	50	80	83
8	350°C	20	20	20	23	26	30	_	_
	400°C	18	18	18	21	23	27	_	_
	Amount of Pt	. 0	0.2	0.3	2	7	10	40	4 3
	Total amount of additional elements	40	40.2	40.3	42	47	50	80	83
19	350°C	21	21	21	24	27	31		_
	400°C	19	19	19	21	24	28		
	Amount of Pt	0	0.2	0.3	2	7	10	37	40
	Total amount of additional elements	43	43.2	43.3	45	50	53	80	83
22	350°C	21	21	22	25	28	_32		
	400°C	19	- 19	19	22	25	29		

TABLE 19 (Ta = 3, N = 2)

Amo	unt of Mn								
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	5	5.2	5.3	8	20	34	64	67
0	350°C	79_	79	80	91	103	119	158	158
	400°C	71	71	72	82	92	107	142	142
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	5.5	5.7	5.8	8	20	34	64	67
0.5	350°C	78	78	79	90	102	117	156	156
	400°C	70	70	71	81	92	106	141	141
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	6	6.2	6.3	8	20	34	64	67
1	· 350°C	75	75	76	86 ·	98	113	150	150
	400°C	68	68	68	78	88	101	135_	135
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	10	10.2	10.3	12	20	34	64	67
5	350°C	71	71	72	82	92	107	142	142
	400°C	64	64	65	74	83	96	128	128
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	13	13.2	13.3	15	20	34	64	67
8	350°C	75	75	76	86	98	113	150	150
	400°C	68	68	68	78	88	101	135	135
	Amount of Pt	0	0.2	0.3	2	7	10	40	43
	Total amount of additional elements	24	24.2	24.3	26	31	34	64	67
19	350°C	77	77	78	89	101	116	155	155
	400°C	70	70	70	80	91	105	139	139
	Amount of Pt	0	0.2	0.3	2	7	10	37	40
	Total amount of additional elements	27	27.2	27.3	29	34	37	64	67
22	350°C	81	81	81	93	105	121	161	161
	400°C	73	73	73	83	94	109	145	145

TABLE 20 (Ta = 14, N = 7)

									
Amo	unt of Mn				. –	<u> </u>			
İ	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	21	21.2	21.3	24	36	50	80	83
0	350°C	38	38	38	44	.49	. 57		<u> </u>
	400°C	34	34	35	39	44	51		_
	Amount of Pt	0	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	21.5	21.7	21.8	24	36	50	80	83
0.5	350°C	38	38	38	43	49	56		
	400°C	34	34	34	39	44	51	_	
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	22	22.2	22.3	24	36	50	. 80	83
1	350°C	36	36	36	42	47	54		
	400°C	32	32	33	37	42	49	_	
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	26	26.2	26.3	28	36	- 50	80	83
5	350°C	34	34	35	39	44	51	_	_
	400°C	31	31	31	35	40	46	_	_
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	29	29.2	29.3	31	36	50	80	83
8	350°C	36	36	36	42	47	54	_	-
	400°C	32	32	33	37	42	49	_	
	Amount of Pt	0.	0.2	0.3	2	7	10	40	43
	Total amount of additional elements	40	40.2	40.3	42	47	50	80	83
19	350°C	37	37	38	43	48	56	_	_
_	400°C	34	34	34	39	44	50	_	_
	Amount of Pt	0.	0.2	0.3	2	7	10	37	40
	Total amount of additional elements	43	43.2	43.3	45	50	53	80	83
22	350°C	39	39	39	45	50	58	_	_
	400°C	35	35_	35	40	45	52		

TABLE 21 (Ta = 29, N = 19)

Amo	unt of Mn			(1a - /	· ·				
	Amount of Pt	0	0.2	0.3	3	15	29	59	62
	Total amount of additional elements	48	48.2	48.3	51	63	77	107	110
0	350°C	5	_ 5	5	6	7			-
	400°C	5	5	5	5	6	-		_
	Amount of Pt	0 -	0.2	0.3	2.5	14.5	28.5	58.5	61.5
	Total amount of additional elements	48.5	48.7	48.8	51	63.	77	107	110
0.5	350°C	5	5	5	6	6			
	400°C	4	4	4	5	6			
	Amount of Pt	0	0.2	0.3	2	14	28	58	61
	Total amount of additional elements	49	49.2	49.3	51	63	77	107	110
1	350°C	5	5	5	5	6	_		-
	400°C	4	4	4	5	6			
	Amount of Pt	0	0.2	0.3	2	10	24	54	57
	Total amount of additional elements	53	53.2	53.3	55	63	77	107	110
5	350°C	5	5	5	5	6	_	_	
	400°C	4	4	4	5	5	_	_	_
	Amount of Pt	0	0.2	0.3	2	7	21	51	54
	Total amount of additional elements	56	56.2	56.3	58	63	77	107	110
8	350°C	5	5	5	5	6	_		_
	400°C	4	4	4	5	6	_		_
	Amount of Pt	0	0.2	0.3	2	7	10	40	43
	Total amount of additional elements	67	67.2	67.3	69	74	77	107	110
19	350°C	5	5	5	6	_	_	_	_
	400°C	4	4	4	5	_	_	_	_
	Amount of Pt	.0	0.2	0.3	2	7	10	37	40
	Total amount of additional elements	70	70.2	70.3	72	77	80	107	110
22	350°C	5	5	5					
	400°C	5	5	5					

TABLE 22 (Ta = 31, N = 21)

Amount of Mn Amount of Pt Total amount of additional elements 0 350°C 4 00°C Amount of Mn 0 0.2 0.3 3 15 29 59 50 67 81 111 0 350°C 5 5 5 5 6 400°C	62 114 — — 61.5 114
Total amount of additional elements 52 52.2 52.3 55 67 81 111 0 350°C 5 5 5 5 6	114 - - 61.5
additional elements 52 52.2 52.3 55 67 81 111 0 350°C 5 5 5 5 6 - -	- 61.5
400°C	
1000 1 1 0 0	
Amount of Pt 0 0.2 0.3 2.5 14.5 28.5 58.5	114
Total amount of additional elements 52.5 52.7 52.8 55 67 81 111	114
0.5 350°C 4 4 4 5 6	
400°C 4 4 4 5 5	
Amount of Pt 0 0.2 0.3 2 14 28 58	61
Total amount of 53 53.2 53.3 55 67 81 111	114
1 350°C 4 4 4 5 6	_
400°C 4 4 4 4 5	
Amount of Pt 0 0.2 0.3 2 10 24 54	57
Total amount of additional elements 57 57.2 57.3 59 67 81 111	114
5 350°C 4 4 4 5 5	
400°C 4 4 4 4 5	
Amount of Pt 0 0.2 0.3 2 7 21 51	54
Total amount of additional elements	114
8 350°C 4 4 5 6	
400°C 4 4 4 4 5	
Amount of Pt 0 0.2 0.3 2 7 10 40	43
Total amount of additional elements 71 71.2 71.3 73 78 81 111	114
19 350°C — — — — — — —	_
400°C	
Amount of Pt 0 0.2 0.3 2 7 10 37	40
Total amount of additional elements 74 74.2 74.3 76 81 84 111	114
22 350°C — — — — — — —	_
400°C	

The invention may be embodied in other forms without departing from the spirit or essential characteristics thereof. The embodiments disclosed in this application are to be considered in all respects as illustrative and not limiting. The scope of the invention is indicated by the appended claims rather than by the foregoing description, and all changes which come within the meaning and range of equivalency of the claims are intended to be embraced therein.

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